



AVX
Surface Mount
Ceramic Capacitor Products

AVX Products Listing



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Power Film Power Ceramic Ceramic Disc Trimmer

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Chips Arrays

Potentiometers

Timing Devices

BestCap™

Resonators Oscillators

Crystals

Filters

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Thin Film

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Fuses
Capacitors
Couplers
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Filters

Integrated Passive

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Low Inductance Chip Arrays

"Z" Chips

Capacitor Arrays
Dual Resonance Chips

Custom IPCs

Voltage Suppressors, Varistors and Thermistors

Acoustical Piezos

Ferrites

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Automotive Connectors

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Custom Designed Connectors

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Harnessing Services
DIN 41612 Connectors
FFC/FPC Connectors

Insulation Displacement Connectors

I/O Connectors

Memory Card Connectors CF, PCMICIA, SD, MMC

MOBO™, I/O, Board to Board and

Battery Connectors
Press-fit Connectors

Varicon®

Wire to Board, Crimp or IDC

For more information please visit our website at

http://www.avxcorp.com

Ceramic Chip Capacitors



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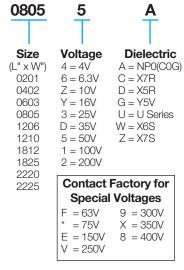
How to Order





Commercial Surface Mount Chips

EXAMPLE: 08055A101JAT2A



Capacitance 2 Sig. Fig + No. of Zeros Examples: 100 = 10 pF 101 = 100 pF 102 = 1000 pF 223 = 22000 pF 224 = 220000 pF 105 = 1µF 106 = 10µF 107 = 100µF For values below 10 pF, use "R"

in place of

Decimal point, e.g.,

9.1 pF = 9R1.

Tolerance $B = \pm .10 \text{ pF}$ $C = \pm .25 \text{ pF}$ $D = \pm .50 \text{ pF}$ $F = \pm 1\% (\ge .25 \text{ pF})$ $G = \pm 2\% (\ge .13 \text{ pF})$ $J = \pm 5\%$ $K = \pm 10\%$ $M = \pm 20\%$

Z = +80%, -20%

P = +100%, -0%

Failure
Rate
A = N/A

lure Terminations ate T = Plated Ni N/A and Sn 7 = Gold Plated

Contact Factory For 1 = Pd/Ag Term Packaging
Available
2 = 7" Reel
4 = 13" Reel
7 = Bulk Cass.

Contact Factory For Multiples

9 = Bulk

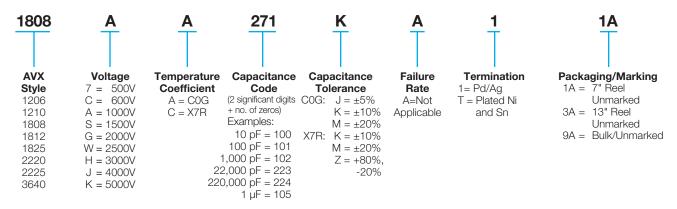
* B, C & D tolerance for ≤10 pF values.

Standard Tape and Reel material (Paper/Embossed) depends upon chip size and thickness.

See individual part tables for tape material type for each capacitance value.

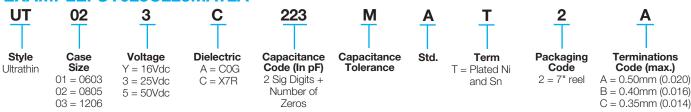
High Voltage Surface Mount Chips

EXAMPLE: 1808AA271KA11A



Ultra Thin Surface Mount Chips

EXAMPLE: UT023C223MAT2A



Please handle these products with due care as they are inherently more fragile than standard MLC capacitors because of their physical dimensions.



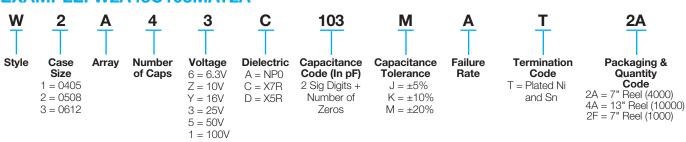
How to Order





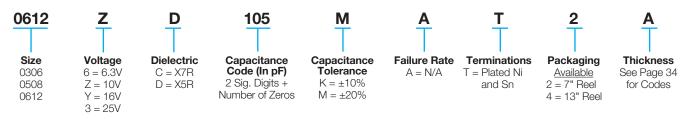
Capacitor Array





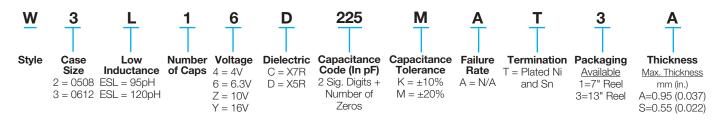
Low Inductance Capacitors (LICC)

EXAMPLE: 0612ZD105MAT2A



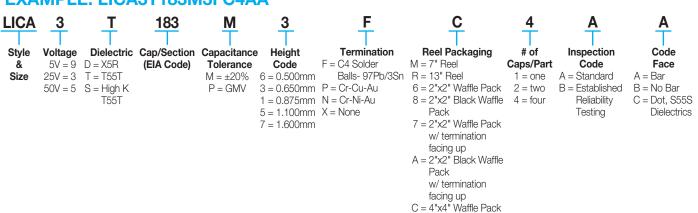
Interdigitated Capacitors (IDC)

EXAMPLE: W3L16D225MAT3A



Decoupling Capacitor Arrays (LICA)

EXAMPLE: LICA3T183M3FC4AA



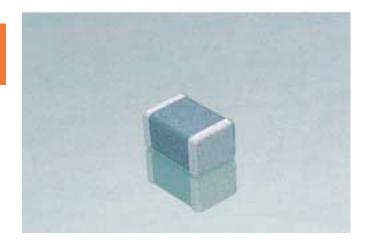


w/ clear lid

COG (NP0) Dielectric

General Specifications



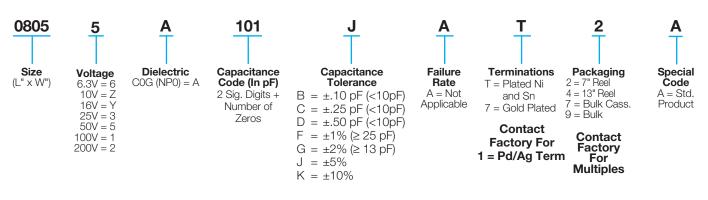


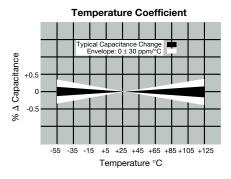
COG (NP0) is the most popular formulation of the "temperature-compensating," EIA Class I ceramic materials. Modern COG (NP0) formulations contain neodymium, samarium and other rare earth oxides.

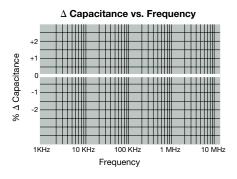
COG (NP0) ceramics offer one of the most stable capacitor dielectrics available. Capacitance change with temperature is 0 $\pm 30 ppm/^{\circ}C$ which is less than $\pm 0.3\%$ Δ C from -55°C to +125°C. Capacitance drift or hysteresis for COG (NP0) ceramics is negligible at less than $\pm 0.05\%$ versus up to $\pm 2\%$ for films. Typical capacitance change with life is less than $\pm 0.1\%$ for COG (NP0), one-fifth that shown by most other dielectrics. COG (NP0) formulations show no aging characteristics.

The COG (NP0) formulation usually has a "Q" in excess of 1000 and shows little capacitance or "Q" changes with frequency. Their dielectric absorption is typically less than 0.6% which is similar to mica and most films.

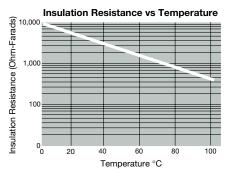
PART NUMBER (see page 2 for complete part number explanation)

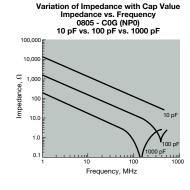


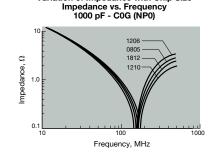


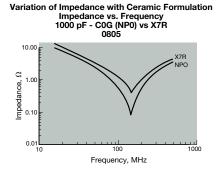


Variation of Impedance with Chip Size











C0G (NP0) Dielectric



Specifications and Test Methods

Parame		NP0 Specification Limits	Measuring	
Operating Temp		-55°C to +125°C	Temperature C	
Capac	itance	Within specified tolerance	Freq.: 1.0 MHz ± 10	
	2	<30 pF: Q≥ 400+20 x Cap Value		% for cap > 1000 pF
	·	≥30 pF: Q≥ 1000 100,000MΩ or 1000MΩ - μF,	Voltage: 1.0 Charge device with	
Insulation I	Resistance	whichever is less	60 ± 5 secs @ roo	
		Willion lovel 15 1635	Charge device with 300	
Dielectric	Strength	No breakdown or visual defects	1-5 seconds, w/charge	
	3.		limited to 50	
	Appearance	No defects	Deflection	
	Capacitance	±5% or ±.5 pF, whichever is greater	Test Time: 3	30 seconds
Resistance to	Variation			1mm/sec
Flexure	Q	Meets Initial Values (As Above)		
Stresses	Insulation			
	Resistance	≥ Initial Value x 0.3	90 1	mm —
		≥ 95% of each terminal should be covered	Dip device in eutectic	solder at 230 + 5°C
Solder	rability	with fresh solder	for 5.0 ± 0 .	
	Appearance	No defects, <25% leaching of either end terminal		
	Capacitance	≤ ±2.5% or ±.25 pF, whichever is greater		
	Variation	2 12.070 of 1.120 pt ; Williottovor to grouter	Dip device in eutectic :	solder at 260°C for 60
Resistance to	Q	Meets Initial Values (As Above)	seconds. Store at room	
Solder Heat	Insulation	Theore will all values y le / les ve/	hours before measurin	
	Resistance	Meets Initial Values (As Above)		
	Dielectric			
	Strength	Meets Initial Values (As Above)		
	Appearance	No visual defects	Step 1: -55°C ± 2°	30 ± 3 minutes
	Capacitance	\leq ±2.5% or ±.25 pF, whichever is greater	Step 2: Room Temp	≤3 minutes
	Variation			
Thermal	Q	Meets Initial Values (As Above)	Step 3: +125°C ± 2°	30 ± 3 minutes
Shock	Insulation			
	Resistance	Meets Initial Values (As Above)	Step 4: Room Temp	≤3 minutes
	Dielectric	NA t - 1 (t - 1 \ / - 1 \ / \ - \ \ \ - \ \ \ - \ \ \ \ \	Repeat for 5 cycles ar	nd measure after
	Strength	Meets Initial Values (As Above)	24 hours at room tem	perature
	Appearance	No visual defects		
	Capacitance	\leq ±3.0% or ± .3 pF, whichever is greater	Charge device with	wise reted veltaria in
	Variation	≥ 30 pF: Q≥ 350	Charge device with to test chamber set	
Load Life	Q	≥ 30 pr.	for 1000 hou	
Loud Liio	(C=Nominal Cap)	<10 pF: Q≥ 200 +10C	101 1000 1100	10 (1 10, 0).
	Insulation		Remove from test cha	amber and stabilize at
	Resistance	≥ Initial Value x 0.3 (See Above)	room temperatu	
	Dielectric	Meets Initial Values (As Above)	before me	easuring.
	Strength	, , ,		
	Appearance Capacitance	No visual defects		
	Variation	\leq ±5.0% or ± .5 pF, whichever is greater	Store in a test chamb	er set at 85°C + 2°C/
	Variation	≥ 30 pF: Q≥ 350	$85\% \pm 5\%$ relative hu	
Load	Q	≥10 pF, <30 pF: Q≥ 275 +5C/2	(+48, -0) with rate	
Humidity		<10 pF: Q≥ 200 +10C		
	Insulation	≥ Initial Value x 0.3 (See Above)	Remove from cham	
	Resistance	2 II III a valdo x 0.0 (000 70000)	room temperature	
	Dielectric	Meets Initial Values (As Above)	before me	easuring.
	Strength	,		



C0G (NP0) Dielectric





PREFERRED SIZES ARE SHADED

 \Box SIZE 0201 0402 0603 0805 1206 Soldering Reflow Only Reflow Only Reflow/Wave Reflow/Wave Reflow/Wave Packaging All Paper Paper/Embossed Paper/Embossed All Paper All Paper 0.60 ± 0.03 (0.024 ± 0.001) 2.01 ± 0.20 (0.079 ± 0.008) 3.20 ± 0.20 (0.126 ± 0.008) L) Length (0.063 ± 0.006) (0.040 ± 0.004) MM 0.50 ± 0.10 0.81 ± 0.15 1.25 ± 0.20 (W) Width (0.011 ± 0.001) (0.020 ± 0.004) (0.032 ± 0.006) (0.049 ± 0.008) (0.063 ± 0.008) 0.25 ± 0.15 (0.010 ± 0.006) 0.50 ± 0.25 (0.020 ± 0.010) 0.50 ± 0.25 (0.020 ± 0.010) 0.15 ± 0.05 (0.006 ± 0.002) (t) Terminal (0.014 ± 0.006) (in.) 16 50 50 100 1.0 G G G (pF) 1.2 G 1.8 С СС С G G G G G G 2.2 G G 3.9 G СС СС G G G G G G G G 6.8 Α 8.2 12 С С G G G G 18 С С G G G G G G G G 22 33 39 С С G G G G С 56 A A G G G G С G G СС СС G G G 120 Ε 150 180 220 G G G G G М М G 390 G 470 560 G 680 820 G G Q 1200 1500 2200 2700 М 3300 М 3900 Ν 4700 5600 6800 8200 Cap М 0.010 М (µF) 0.012 0.022 0.027 0.039 0.047 0.068 0.082 WVDC 100 100 100 200 SIZE 0201 0402 0603 0805 1206 Letter CC 0.33 0.56 0.71 0.86 0.94 1.40 1.52 2.29 2.54 2.79 3.175 (0.028)(0.034)(0.040)(0.070)(0.090)**PAPER EMBOSSED**

Contact Factory for Multiples



C0G (NP0) Dielectric



Capacitance Range

PREFERRED SIZES ARE SHADED

			П		J.		 	П										
SIZ	'F			 210			18	12			1825			2220			2225	
Solde				//Wave			Reflow			-	Reflow On	lv	R	leflow Only	V		Reflow Or	nlv
Packa			Paper/E	mbossed			All Emb	ossed			II Emboss			l Embosse		A	All Emboss	sed
(L) Length	MM (in.)			± 0.20 ± 0.008)			4.50 ± (0.177 ±			((4.50 ± 0.30 0.177 ± 0.01			5.70 ± 0.40 224 ± 0.016			5.72 ± 0.25 0.225 ± 0.01	
(W) Width	MM		2.50	± 0.20			3.20 ±	0.20			6.40 ± 0.40)		5.00 ± 0.40	·		6.35 ± 0.25	5
(t) Terminal	(in.) MM			± 0.008) ± 0.25			(0.126 ±				$0.252 \pm 0.0^{\circ}$ 0.61 ± 0.36			197 ± 0.016 0.64 ± 0.39			0.250 ± 0.01 0.64 ± 0.39	
(i) Terminal WVD	(in.)	25	(0.020	± 0.010)	200	25`	(0.024 ±	100	200	50	0.024 ± 0.01	200	(0. 50	025 ± 0.015	5) 200	50	0.025 ± 0.01	15) 200
Cap (pF)	0.5 1.0 1.2 1.5 1.8 2.2 2.7	20	30	100	200	23	30	100	200	30	100	200	30	100	200	30		W~
	2.2 2.7 3.3 3.9 4.7 5.6																	
	6.8 8.2															* t	1	
	10 12 15																	
	18 22 27																	
	33 39 47																	
	56 68																	
	82 100 120 150																	
	180 220 270																	
	330 390 470																	
	560 680 820	J J	J	J	J J													
	1000 1200 1500	J J	J	J	J M M	K K K	K K K	K K K	K K K	M M M	M M M	M M M	X X X	X X X	X X X	P P P	P P P	P P P
	1800 2200 2700	J J	J	J M M	M Q Q	K K K	K K K	K K K	K K P	M M M	M M M	M M M	X X X	X X X	X X X	P P P	P P P	P P P
	3300 3900 4700	J J	JJ	M M M		K K K	K K K	K K K	P P P	M M M	M M M	M M M	X X X	X X X	X X X	P P P	P P P	P P P
	5600 6800 8200	J	JJ	M M		K K	M M P	M M X	P X X	M M M	M M M	M M	X X X	X X X	X X X	P P P	P P	P P
Cap (µF)	0.010 0.012 0.015	N N	N N			K K M	P P P	X X X	Χ	M M P	M M M		X X X	X X X	X X X	P P P	P P P	P P Y
	0.018 0.022 0.027					M M M	P CC CC			P P P	M		X X X	X X X	X	P P P	P	Y
	0.033 0.039					M M	CC CC CC			P P P			X	X		P P P	Y	Y
	0.047 0.068 0.082					CC CC CC	CC CC CC			P						P P P		
WVD	0.1 IC	25	50	100	200	25	50	100	200	50	100	200	50	100	200	50	100	200
SIZ				10			18				1825			2220			2225	
Letter	Α	С		E	G	J	K	М		N	Р	Q	X	Y		Z	ВВ	CC
Max. Thickness	0.33 (0.013)	0.56		.71 028) (0.86	0.94 (0.037)	1.02 (0.040)	(0.05		.40 055)	1.52 (0.060)	1.78 (0.070)	2.29 (0.090)	2.54		.79 110) (3.05 (0.120)	3.175 (0.125)
	(5.0.0)	(0.02	, ,	PER	, ,	(5.50.)	(2.0.0)	(0.00	-, (3.	,	(, ,	SSED	(00	., [3.			(520)

Contact Factory for Multiples



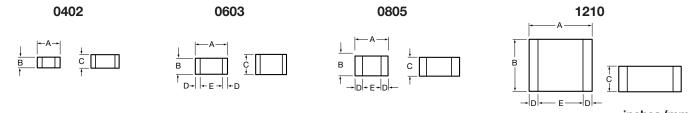
COG (NP0) Capacitors for RF/Microwave



GENERAL INFORMATION

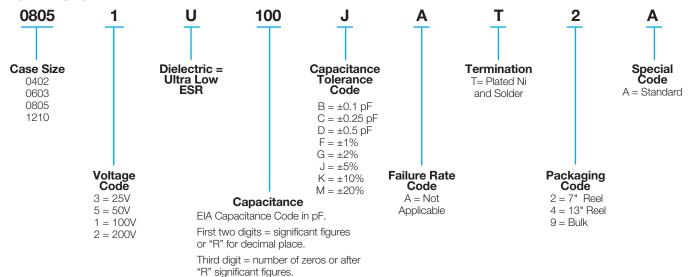
"U" Series capacitors are COG (NPO) chip capacitors specially designed for "Ultra" low ESR for applications in the communications market. Max ESR and effective capacitance are met on each value producing lot to lot uniformity. Sizes available are EIA chip sizes 0603, 0805, and 1210.

DIMENSIONS: inches (millimeters)



					inches (mm)
Size	Α	В	С	D	E
0402	$0.039 \pm 0.004 (1.00 \pm 0.10)$	$0.020 \pm 0.004 (0.50 \pm 0.10)$	0.024 (0.60) max.	N/A	N/A
0603	$0.060 \pm 0.010 (1.52 \pm 0.25)$	$0.030 \pm 0.010 (0.76 \pm 0.25)$	0.036 (0.91) max.	0.010 ± 0.005 (0.25 ± 0.13)	0.030 (0.76) min.
0805	$0.079 \pm 0.008 (2.01 \pm 0.20)$	$0.049 \pm 0.008 (1.25 \pm 0.20)$	$0.040 \pm 0.005 (1.02 \pm 0.127)$	$0.020 \pm 0.010 (0.51 \pm 0.255)$	0.020 (0.51) min.
1210	0.126 ± 0.008 (3.2 ± 0.20)	$0.098 \pm 0.008 (2.49 \pm 0.20)$	$0.050 \pm 0.005 (1.27 \pm 0.127)$	$0.025 \pm 0.015 \ (0.635 \pm 0.381)$	0.040 (1.02) min.

HOW TO ORDER



ELECTRICAL CHARACTERISTICS

Capacitance Values and Tolerances:

Size 0402 - 0.2 pF to 22 pF @ 1 MHz Size 0603 - 1.0 pF to 100 pF @ 1 MHz Size 0805 - 1.6 pF to 160 pF @ 1 MHz Size 1210 - 2.4 pF to 1000 pF @ 1 MHz

Temperature Coefficient of Capacitance (TC):

 $0 \pm 30 \text{ ppm/°C } (-55^{\circ} \text{ to } +125^{\circ}\text{C})$

Insulation Resistance (IR):

 $10^{12} \Omega$ min. @ 25°C and rated WVDC 10 $^{\scriptscriptstyle 11}$ Ω min. @ 125°C and rated WVDC

Working Voltage (WVDC):

Size

Working Voltage 50 WVDC 0603 -200, 100, 50 WVDC 0805 -200, 100 WVDC 1210 -200, 100 WVDC

Dielectric Working Voltage (DWV):

250% of rated WVDC

Equivalent Series Resistance Typical (ESR):

0402 - See Performance Curve, page 9 See Performance Curve, page 9 See Performance Curve, page 9 See Performance Curve, page 9

Marking: Laser marking EIA J marking standard (except 0603) (capacitance code and

tolerance upon request).

MILITARY SPECIFICATIONS

Meets or exceeds the requirements of MIL-C-55681



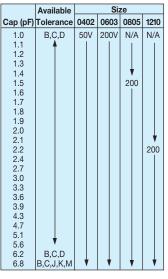
C0G (NP0) Capacitors for RF/Microwave

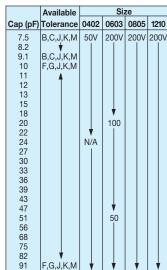


Ultra Low ESR, "U" Series, C0G (NP0) Chip Capacitors

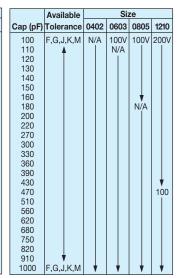
CAPACITANCE RANGE

	Available		Siz	ze	
Cap (pF)	Tolerance	0402	0603	0805	1210
0.2	B,C	50V	N/A	N/A	N/A
0.3	À				
0.4					
0.5	B,C				
0.6	B,C,D				
0.7	A				
0.8					
0.9	B,Ċ,D	*	♦	♥	*
	0.2 0.3 0.4 0.5 0.6 0.7	Cap (pF) Tolerance 0.2 0.3 0.4 0.5 B,C 0.6 B,C,D 0.7 0.8	Cap (pF) Tolerance 0402 0.2 B,C 50V 0.3 ↓ , 0.4 B,C , 0.6 B,C,D , 0.7 ↓ , 0.8 ↓ ,	Cap (pF) Tolerance 0402 0603 0.2 B,C 50V N/A 0.3 A	Cap (pF) Tolerance 0402 0603 0805 0.2 B,C 50V N/A N/A 0.5 B,C 0.6 B,C,D 0.7 0.8 V A A A A A A A A A A A A A A A A A A



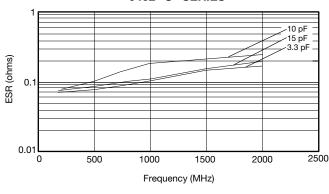


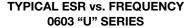
F,G,J,K,M

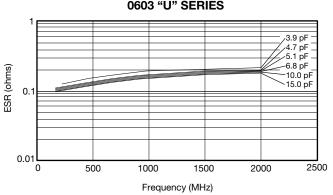


ULTRA LOW ESR, "U" SERIES

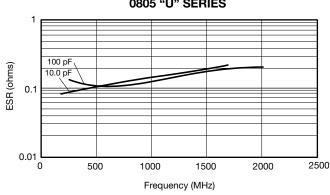
TYPICAL ESR vs. FREQUENCY 0402 "U" SERIES



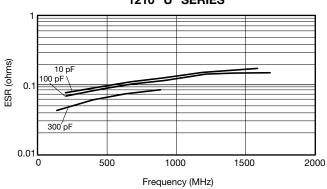




TYPICAL ESR vs. FREQUENCY 0805 "U" SERIES



TYPICAL ESR vs. FREQUENCY 1210 "U" SERIES

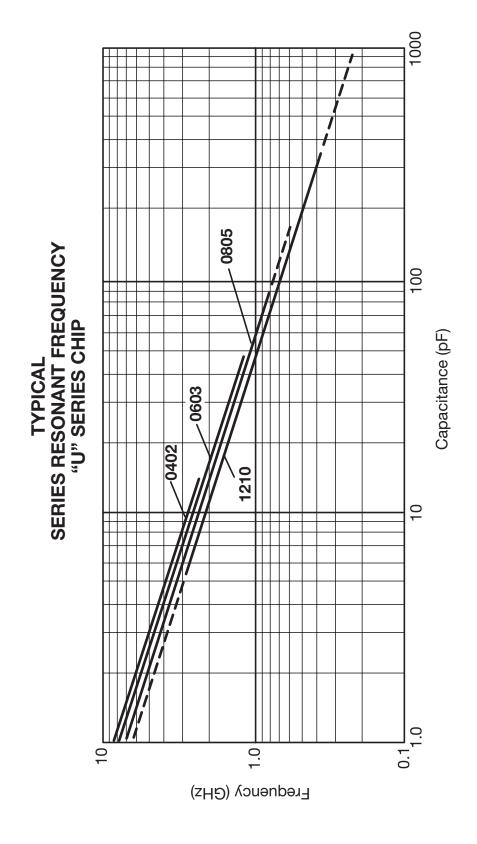


ESR Measured on the Boonton 34A

C0G (NP0) Capacitors for RF/Microwave

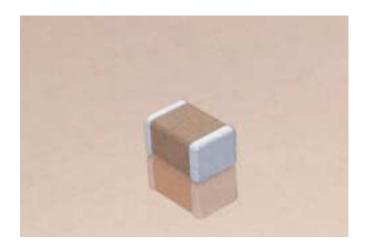


Ultra Low ESR, "U" Series, C0G (NP0) Chip Capacitors



General Specifications



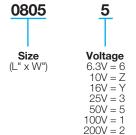


X7R formulations are called "temperature stable" ceramics and fall into EIA Class II materials. X7R is the most popular of these intermediate dielectric constant materials. Its temperature variation of capacitance is within ±15% from -55°C to +125°C. This capacitance change is non-linear.

Capacitance for X7R varies under the influence of electrical operating conditions such as voltage and frequency.

X7R dielectric chip usage covers the broad spectrum of industrial applications where known changes in capacitance due to applied voltages are acceptable.

PART NUMBER (see page 2 for complete part number explanation)





103 Capacitance Code (In pF) 2 Sig. Digits + Number of Zeros

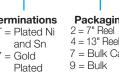


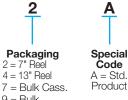
 $M = \pm 20\%$



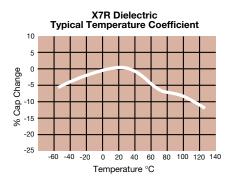


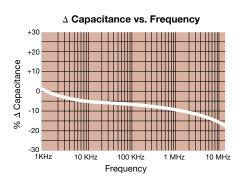
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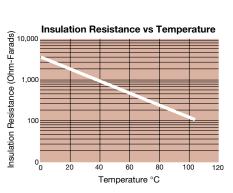




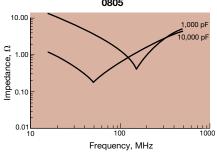
Contact **Factory For** Multiples

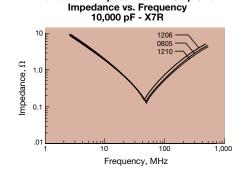






Variation of Impedance with Cap Value Impedance vs. Frequency 1,000 pF vs. 10,000 pF - X7R 0805





Variation of Impedance with Chip Size

Impedance vs. Frequency 100,000 pF - X7R Impedance, Ω 0. .01 Frequency, MHz

Variation of Impedance with Chip Size





Specifications and Test Methods

Parame		X7R Specification Limits	Measuring	
Operating Temp		-55°C to +125°C	Temperature C	Cycle Chamber
Capac	itance	Within specified tolerance		
		\leq 2.5% for \geq 50V DC rating	Freq.: 1.0 k	
Dissipation	on Factor	≤ 3.0% for 25V DC rating	Voltage: 1.0	
•		≤ 3.5% for 16V DC rating ≤ 5.0% for ≤ 10V DC rating	For Cap $> 10 \mu F$, (J.5Vrms @ 120HZ
		$\leq 3.0\%$ for ≤ 100 DC rating $= 100,000$ MΩ or $= 1000$ MΩ - $= \mu$ F,	Charge device with	n rated voltage for
Insulation I	Resistance	whichever is less	60 ± 5 secs @ roc	
Dielectric	Strength	No breakdown or visual defects	Charge device with 300 1-5 seconds, w/charge limited to 50	0% of rated voltage for and discharge current 0 mA (max)
	Appearance	No defects	Deflection	
	Capacitance	≤ ±12%	Test Time: 3	30 seconds
Resistance to	Variation	:_,;		1mm/sec
Flexure	Dissipation	Meets Initial Values (As Above)		
Stresses	Factor	1110010 11 111011 7 011000 (10 7 10010)		
	Insulation Resistance	≥ Initial Value x 0.3	901	mm —
		≥ 95% of each terminal should be covered	Dip device in eutection	
Solder	rability	with fresh solder	for 5.0 ± 0 .	
	Appearance	No defects, <25% leaching of either end terminal	10. 0.0 = 0.	0 00001100
	Capacitance	≤ ±7.5%		
	Variation	≤ ±1.570	Dip device in eutectic :	colder at 260°C for 60
Resistance to	Dissipation	Meets Initial Values (As Above)	seconds. Store at room	
Solder Heat	Factor	IVICES ITILIAI VAIUES (AS ADOVE)	hours before measurin	
	Insulation	Meets Initial Values (As Above)		9 0.001.00. p. op 0. 1.00.
	Resistance Dielectric			
	Strength	Meets Initial Values (As Above)		
	Appearance	No visual defects	Step 1: -55°C ± 2°	30 ± 3 minutes
	Capacitance	≤ ±7.5%	Step 2: Room Temp	≤3 minutes
	Variation	≤±1.5/6	Step 2. Noon Temp	2 3 minutes
Thermal	Dissipation	Meets Initial Values (As Above)	Step 3: +125°C ± 2°	30 ± 3 minutes
Shock	Factor	Wicets illitial values (No / Nove)	Otop 0. 1120 O ± 2	00 ± 0 11iii idt03
	Insulation Resistance	Meets Initial Values (As Above)	Step 4: Room Temp	≤ 3 minutes
	Dielectric	,	Repeat for 5 cycles ar	nd maggira after
	Strength	Meets Initial Values (As Above)	24 ± 2 hours at room	
	Appearance	No visual defects	2122110010 00100111	10111 001041010
	Capacitance	≤±12.5%	Charge device with t	
	Variation	3 112.070	test chamber set	
	Dissipation	≤ Initial Value x 2.0 (See Above)	for 1000 hou	urs (+48, -0)
Load Life	Factor	= 11 mad value x 2.0 (000 / 100 vo)	Davis ava frans to at al	a coole ou a co al atala ilima
	Insulation	≥ Initial Value x 0.3 (See Above)	Remove from test ch at room temperatu	
	Resistance Dielectric	, ,	before me	
	Strength	Meets Initial Values (As Above)	0010101111	Sadding.
	Appearance	No visual defects	Ohomo in a tarih i	arrant at 0500 × 000/
	Capacitance	≤ ±12.5%	Store in a test chamb 85% ± 5% relative hu	
	Variation	⊇ ±12.∪/0	(+48, -0) with rate	
Load	Dissipation	≤ Initial Value x 2.0 (See Above)	(1 70, -0) WILLIALE	a voltago applica.
Humidity	Factor	= 11 11101 V C100 / 2.0 (000 / 100 VO)	Remove from cham	ber and stabilize at
	Insulation	≥ Initial Value x 0.3 (See Above)	room temperature	
	Resistance Dielectric	(24 ± 2 hours be	
	Strength	Meets Initial Values (As Above)		
	ou ongui			







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SIZE	E	02	01			0402						0603						08	05					12	06		
Solder	ing	Reflov	v Only		Ref	flow O	nly				Ref	low/W	ave				ı	Reflow	/Wave				ı	Reflow	/Wave		
Packag		All P				II Pape						II Pape					Pa	per/Er		ed			Pa		nbosse	ed	
(L) Length	MM (in.)		± 0.03 ± 0.001)			00 ± 0.1 40 ± 0.0						60 ± 0.1 63 ± 0.0					((2.01 ± 0.079 ±							± 0.20 ± 0.008		
(W) Width	MM	0.30 -	± 0.03		0.5	50 ± 0.1	0				0.8	81 ± 0.1	5					1.25 ±	0.20					1.60	± 0.20		
-	(in.) MM	0.011 :	± 0.001)			20 ± 0.0 25 ± 0.1	- '					32 ± 0.0 35 ± 0.1					(0.049 ±							± 0.008) ± 0.25)	
(t) Terminal	(in.)		± 0.002)			10 ± 0.0						4 ± 0.0					(1	0.020 ±						(0.020 :	± 0.010)	
WVDC Cap	100	10 A	16 A	6.3	10	16	25 C	50	6.3	10	16	25	50	100	200	10	16	25	50	100	200	10	16	25	50	100	200
(pF)	120 150	A	A	CCC	CCC	CCC	CCC	000																			
	180 220	A A	A	CCC	000	CCC	CCC	000	G G	G G	G G	G G	G G	G G	G G	_	_			_	_		>			-W	
	270 330	A	A				С		G	G	G	G	G		G	E	E	E	E	E	E	× (نے (را	Т
	390 470	A A	A	CCC	000	CCC	C	000	G G	G G G	G G	G G G	G G	GGG	G G	E	E E	E E	E	E E E	E E	(_) [- سا	<u> </u>
	560 680	A A	A A	CCC	CCC	CCC	C	000	G G	G G G	G G	G G G	G G G	G G	G G	E	E E	E	E E E	E E E	E			مجه ا			
	820 1000	A	A				C	Č C	G G	Ğ	G	Ğ	Ğ		G G	E	E	E E		_		J	J	الا	J	J	J
	1200 1500			CCC	CCC	CCC	CCC	000	G G	G G	G G	G G	G G	G G		E	E E	E E	E E E	E E E	EJJ	J	J	J	J	J	J
	1800 2200 2700			CCC	000	CCC	CCC	000	G G	G G G	G G	G G G	G G	G G		E E	E E E	E E E	E E	E E E	J	J J	J J	J J J	J	J J J	J
	3300 3900			CCC	CCC	000	С	О	G	G G G	G G G	G G G	G	G G G		E	Е	Е	Е	E	J	J	J	J	J	J	J
	4700 5600			C		C	C	000	G G	Ğ	Ğ	Ğ	G G G				E E E	E E	E E E	J	Ĵ	J	Ĵ	J	Ĵ	J J	J
	6800 8200			Ċ	CCC	CCC	C		G G	G G G	G G	G G	G	G G		E E	E	E E	Е	J	J	J	J	J	J	J	J
Cap. (µF)	0.010 0.012 0.015			000	CCC	CCC			G G	G G G	GGG	G G	GGG	G G		E J J	E J J	E J J	E J J	J J	J	J J	J J	J J	J	J J J	J M M
	0.018 0.022			C	CCC	CC			G G	G G G	G G	G G G	G G			J	J	J	J	J	M M	J	J	J	J	J	M M
	0.027			C	C				G	G	G	G	G			J	J	J	J	J		J	J	J	J	J	M
	0.039 0.047			С	С				G G	Ğ	G G	G G	G			J	J	J	J	M M		J	J	J	J	J	M
	0.056 0.068 0.082								G G	G G G	G G	G G				J J	J	J J	J			J	J J J	J	J	J J M	P P
	0.10 0.12								G	G	G	G				J	J	J	J			J	J	J	J	M	
	0.15 0.18								G	G G						Ĵ	Ĵ	J M				J	Ĵ	J	Ĵ		
	0.22 0.27								G	G						J M	J M	М				J	J	J	J		
	0.33 0.47															M N	M M					J	J	M M	M M		
	0.56															N N						M	M	Q			
	0.82 1.0															N N						M M	M M	Q Q			
	1.2 1.5 1.8																					P P P					
	2.2																					Q					
	4.7			_																		_				_	
	22 47 100																										
WVDC	100	10	16	6.3	10	16	25	50	6.3	10	16	25	50	100	200	10	16	25	50	100	200	10	16	25	50	100	200
SIZ	E	_	01			0402						0603						080						12			
Letter	Α		С	Е		G		J		K		М		N	-	P	Q		Х		Υ		Z		BB	0	C
Max.	0.33	0	.56	0.7	1	0.86		0.94		1.02		1.27	1	.40	1.8	52	1.7	8	2.29		2.54		2.79		3.05	3.1	175
Thickness	(0.013)	(0.	022)	(0.02		(0.03	4)	(0.037)	(0.040)) (C).050)	(0.	055)	(0.0	060)	(0.07		(0.09	0)	(0.100) (0.110)	(C).120)	(0.1	125)
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Contact Factory for Multiples





Capacitance Range

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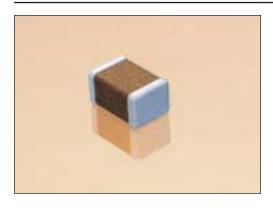
SIZE				1210				18	12		18	25		2220		22	25
Soldering				eflow/Wav				Reflov			Reflov			Reflow On			v Only
Packagin	~			er/Embos	sed			All Eml			All Emb		F	All Emboss		All Eml	
(L) Length	MM (in.)			3.20 ± 0.20 .126 ± 0.00	3)				± 0.30 ± 0.012)		4.50 ± (0.177 ±		(1	5.7 ± 0.40 0.224 ± 0.01			± 0.25 ± 0.010)
(W) Width	MM			2.50 ± 0.20					± 0.20		6.40 ±		//	5.0 ± 0.40			± 0.25
(t) Terminal	(in.) MM			0.098 ± 0.008 0.50 ± 0.25					± 0.008) ± 0.36		(0.252 ± 0.61 ±		(0.197 ± 0.01 0.64 ± 0.39			± 0.010) ± 0.39
	(in.)	40		.020 ± 0.010	· -	100	40		± 0.014)	400	(0.024 ±		_	0.025 ± 0.01		_	± 0.015)
(pF) 1	00 20 50	10	16	25	50	100	16	25	50	100	50	100	50	100	200	50	100
2	80 20 70															≪W	>
3	30 90													(\leq) <u>†</u> T
- 5	70 60													-	بر		
	80 20	J	J	J	J	J									* t		
12 15	00 00	J	J	J	J	J											
18 22 27	00	J J	J J	J J	J	J J											
33 39	00 00	J	J	J	J	J											
<u>47</u> 56	00	J	J	J	J	J											
68 82 Cap.		J J	J	J	J	J			K	K	M	M	Y	Y	Y	M	M
(μF)	0.012 0.015	J J	J	Ĵ	Ĵ	J			K K	K K	M M	M M	X X X	X X X	X X X	M M	M M
	0.018 0.022 0.027	J J	J	J J	J	J			K K K	K K K	M M M	M M M	X X X	X X	X X X	M M M	M M M
	0.033 0.039	J	J	J	J	J			K K	K K	M M	M M	X	X	X	M M	M M
	0.047 0.056 0.068	J J	J J	J	J	J			K K K	K K K	M M M	M M M	X X	X	X X X	M M M	M M M
	0.082	J	J	J	J	J			K K	K K	M M	M M	X	X	X	M M	M M
	0.12 0.15 0.18	J	J	J	J	M M P			K K	K K	M M	M M	X X	X X	X X	M M	M M M
	0.22 0.27	J	J	J J	Ĵ	P Z			K K	K M	M M	M M	X	X	X	M M	M M
	0.33 0.47 0.56	J M M	J M M	M M	J M	Z Z Z			K K M	M P Q	M M M	M M M	X X X	X X		M M M	M M M
	0.68 0.82	M M	M M	P P P	V	Z			M M	X	M M	QQ	X	Х		M M	M M
	1.0 1.2 1.5	N N N	N N N	P	X	Z		М	М	X	M M M	Q	X			M M M	P P
	1.8	N	P	X										Z		M M	
	3.3 4.7	Q	Z				Z										
1	22 47 00																
WVDC	-	10	16	25	50	100	16	25	50	100	50	100	50	100	200	50	100
SIZE				1210			<u> </u>	1812			182		<u> </u>	2220			25
Letter Max.	A	0.56	0.7		G	J 0.94	K	M 1.27	N 1.40	1.52	Q		X	Y 2.54	Z 2.79	BB 3.05	CC 3.175
	(0.013)	(0.022				0.94	(0.040)	(0.050)	(0.055)	(0.060				(0.100)	(0.110)	(0.120)	(0.125)
		1 ,	PAP		, , ,		/	,,	,,	,,,,,,,,		MBOSSE		,		, , ,	,,

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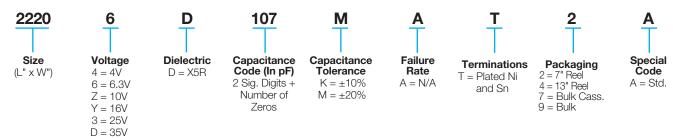
General Specifications



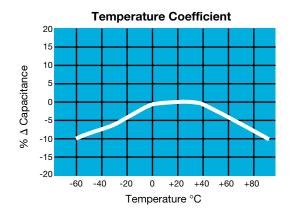
GENERAL DESCRIPTION

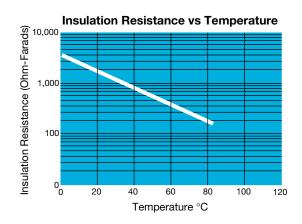
- General Purpose Dielectric for Ceramic Capacitors
- EIA Class II Dielectric
- Temperature variation of capacitance is within ±15% from -55°C to +85°C
- Well suited for decoupling and filtering applications
- Available in High Capacitance values (up to 100μF)

PART NUMBER (see page 2 for complete part number explanation)



TYPICAL ELECTRICAL CHARACTERISTICS







Specifications and Test Methods

Parame	ter/Test	X5R Specification Limits	Measuring	
Operating Temp		-55°C to +85°C	Temperature C	Cycle Chamber
Capac	itance	Within specified tolerance		
		≤ 2.5% for ≥ 50V DC rating	Freq.: 1.0 k	
Dissipation	on Factor	≤ 3.0% for 25V DC rating	Voltage: 1.0	
		≤ 3.5% for 16V DC rating	For Cap > 10 μF,	0.5Vrms @ 120Hz
		≤ 5.0% for ≤ 10V DC rating		
Insulation I	Resistance	100,000M Ω or 500M Ω - μF,	Charge device with	
		whichever is less	60 ± 5 secs @ roo	
Dielectric	Strength	No breakdown or visual defects	Charge device with 300 1-5 seconds, w/charge limited to 50	and discharge current 0 mA (max)
	Appearance	No defects	Deflection	
	Capacitance	≤ ±12%	Test Time: 3	30 seconds
Resistance to	Variation	==:=/0		7 1mm/sec
Flexure Stresses	Dissipation Factor	Meets Initial Values (As Above)	V	
300555	Insulation			
	Resistance	≥ Initial Value x 0.3	90 1	mm —
		≥ 95% of each terminal should be covered	Dip device in eutection	solder at 230 + 5°C
Solder	rability	with fresh solder	for 5.0 ± 0.0	
	Appearance	No defects, <25% leaching of either end terminal		
	Capacitance	≤ ±7.5%		
	Variation	3 11.570	Dip device in eutectic	solder at 260°C for 60
Resistance to	Dissipation	Meets Initial Values (As Above)	seconds. Store at room	
Solder Heat	Factor	Wieets Itiliai Values (As Above)	hours before measurin	
00.00	Insulation	Meets Initial Values (As Above)		9 0.001.104. p. 0p 0. 1.001
	Resistance	177000 11 maa. 7 a.aoo (10 7 100 10)	•	
	Dielectric Strength	Meets Initial Values (As Above)		
	Appearance	No visual defects	Step 1: -55°C ± 2°	30 ± 3 minutes
	Capacitance		·	
	Variation	≤ ±7.5%	Step 2: Room Temp	≤3 minutes
Thermal	Dissipation	Moote Initial Values (As Above)	Step 3: +85°C ± 2°	30 ± 3 minutes
Shock	Factor	Meets Initial Values (As Above)	Step 3: +65°C ± 2°	30 ± 3 minutes
oo	Insulation	Meets Initial Values (As Above)	Step 4: Room Temp	≤3 minutes
	Resistance Dielectric		Repeat for 5 cycles ar	
	Strength	Meets Initial Values (As Above)	24 ± 2 hours at room	
	Appearance	No visual defects	24 ± 2 110013 0t 100111	torriporaturo
	Capacitance	≤ ±12.5%	Charge device with t	wice rated voltage in
	Variation	≤±12.5%	test chamber se	
	Dissipation	≤ Initial Value x 2.0 (See Above)	for 1000 hou	urs (+48, -0)
Load Life	Factor	S Il Illiai Value X 2.0 (See Above)		
	Insulation	≥ Initial Value x 0.3 (See Above)	Remove from test ch	
	Resistance		at room temperatu before me	
	Dielectric Strength	Meets Initial Values (As Above)	Delote ITI	easuring.
	Appearance	No visual defects		
	Capacitance		Store in a test chamb	
	Variation	≤ ±12.5%	$85\% \pm 5\%$ relative hu	
Load	Dissipation	< Initial Value x 2.0 (See Above)	(+48, -0) with rate	u voitage applied.
Humidity	Factor	≤ Initial Value x 2.0 (See Above)	Remove from cham	her and stabilize at
	Insulation	≥ Initial Value x 0.3 (See Above)	room temperature	
	Resistance		24 ± 2 hours be	
	Dielectric Strongth	Meets Initial Values (As Above)		Ŭ
	Strength	<u>'</u>		







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SI	ZE	0201		04	02			(0603					080)5				1206	6				12	10				18	12		2220
Sold	ering	Reflow Only		Reflov	v Only	,		Refle	ow/Wa	ave			R	eflow/	Wave			Refl	ow/W	lave		Г	Re	eflow	/Wav	ve		F	Reflow	v Only	/	Reflow Only
Pack	aging	All Paper		All P	aper				Pape				Pap	er/Em	bosse	ed		Paper						er/Er					l Emb			All Embossed
(L) Lenç	, (In.)	0.60 ± 0.03 (0.024 ± 0.001)	,	0.040	± 0.10)4)		(0.06	$0 \pm 0.$ $3 \pm 0.$	006)			(0.	2.01 ± 079 ±	0.008)		(0.12	0 ± 0. 6 ± 0.	.008)			(0.	1.20 ±	0.00	08)		(0.	4.50 ± 177 ±	0.01	2)	5.70 ± 0.40 (0.225 ± 0.016)
(W) Widt	h MM (in.)	0.30 ± 0.03 (0.011 ± 0.001)			± 0.10				1 ± 0. 2 ± 0.					1.25 ± 049 ±)			$0 \pm 0.$ $3 \pm 0.$					1.50 ±					3.20 ± 126 ±			5.00 ± 0.40 (0.197 ± 0.016)
(t) Tern	MM lenin	0.15 ± 0.05		0.25	± 0.15	,		0.3	5 ± 0.	15			C).50 ±	0.25			0.5	0 ± 0 .	.25			C).50 ±	0.25	5			0.61 ±	0.36		0.64 ± 0.39
(4)	(In.)	(0.006 ± 0.002)	_		± 0.00			_	4 ± 0.		0.5	0.0		020 ±			0.0		0 ± 0 .		0.5	ļ.,		020 ±			l 05	_	024 ±		_	(0.025 ± 0.015)
	WVDC	10	4	6.3	10	16	4	6.3	10	16	25	6.3	10	16	25	35	6.3	10	16	25	35	4	6.3	10	16	25	35	6.3	10	16	25	6.3
Cap (pF)	100 150 220																															
	330 470 680																											_ ا	_ا_	>	>	₩,
	1000 1200	A																										_	(\leq	\supset	
	1500 1800 2200	A A A																												_		
	2700 3300	A A																				\vdash										
	3900 4700 5600	A A A	L				_																							-		
	6800 8200	A A																														
Cap. (µF)	0.010 0.012 0.015	А																														
	0.018 0.022 0.027				С	С																										
	0.033 0.039				CCC	CCC																										
	0.047 0.056 0.068				CCC	С	\vdash				G											\vdash						\vdash				
	0.082			С	C	С					G G																					
	0.12 0.15			CC						G G	G G																					
	0.18 0.22 0.27			C				G G	G G	G G G	G J					N																
	0.33 0.47 0.56							G G	G G	GGG				N N N	N N					М	Q											
	0.68 0.82		0					G G G	G G	G G G				N N	N					M M	_											_
	1.0 1.2 1.5		С					G G	G	G			N N N	N	N				QQQ	Q	Q	\vdash										
	1.8		_				_	G				L					L		ã	_		<u> </u>	Ш			\ \	7			_		
	2.2 3.3 4.7						J	G				N	N N N					QQ	Q Q	Q				Q	Q	Z	Z					
	6.8 10 22		\vdash				\vdash					N					Q Q	Q	Q			\vdash	X Z Z	X Z	X	X			Z	\dashv	Ζ	
	47 100																Q					Z	Z					Z BB				Z
	WVDC	10	4	6.3	10	16	4	6.3	10	16	25	6.3	10	16	25	35	6.3	10	16	25	35	4	6.3	10	16	25	35	6.3	10	16	25	6.3
SI	ZE	0201		04	02			(603					080)5				1206	6				12	10				18	12		2220

Letter	Α	С	Е	G	J	K	M	N	Р	Q	Х	Υ	Z	BB	CC
Max.	0.33	0.56	0.71	0.86	0.94	1.02	1.27	1.40	1.52	1.78	2.29	2.54	2.79	3.05	3.175
Thickness	(0.013)	(0.022)	(0.028)	(0.034)	(0.037)	(0.040)	(0.050)	(0.055)	(0.060)	(0.070)	(0.090)	(0.100)	(0.110)	(0.120)	(0.125)
			PAPER							EMBO	SSED				

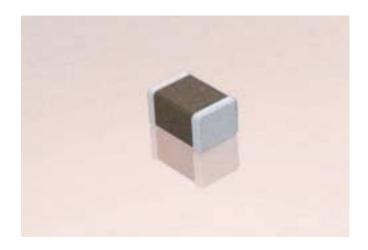
Contact Factory for Multiples



Y5V Dielectric







Y5V formulations are for general-purpose use in a limited temperature range. They have a wide temperature characteristic of +22% -82% capacitance change over the operating temperature range of -30°C to +85°C.

Y5V's high dielectric constant allows the manufacture of the highest capacitance value in a given case size.

These characteristics make Y5V ideal for decoupling applications within limited temperature range.

PART NUMBER (see page 2 for complete part number explanation)





25V = 3

50V = 5

G

Dielectric Y5V = G

104

Capacitance Code (In pF) 2 Sig. Digits + Number of Zeros



Capacitance Tolerance Z = +80 -20%

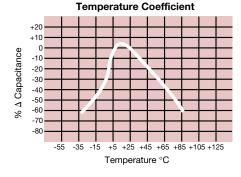


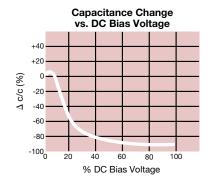
Rate A = NotApplicable

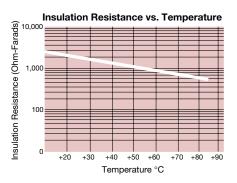


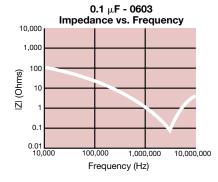


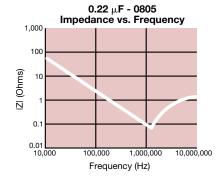


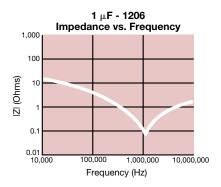














Y5V Dielectric



Specifications and Test Methods

Parame	ter/Test	Y5V Specification Limits	Measuring	
Operating Temp		-30°C to +85°C	Temperature C	Cycle Chamber
Capac Dissipation		Within specified tolerance ≤ 5.0% for ≥ 50V DC rating ≤ 7.0% for 25V DC rating ≤ 9.0% for 16V DC rating	Freq.: 1.0 k Voltage: 1.0 For Cap > 10 μF, k	Vrms ± .2V
		≤ 12.5% for ≤ 10V DC rating	, , ,	
Insulation I	Resistance	100,000M Ω or 500M Ω - μF, whichever is less	Charge device with 60 ± 5 secs @ roo	om temp/humidity
Dielectric	Strength	No breakdown or visual defects	Charge device with 300 1-5 seconds, w/charge limited to 50	and discharge current
	Appearance	No defects	Deflection	
	Capacitance	≤ ±30%	Test Time: 3	30 seconds
Resistance to	Variation	= ±00/0	\	7 1mm/sec
Flexure Stresses	Dissipation Factor	Meets Initial Values (As Above)		
	Insulation Resistance	≥ Initial Value x 0.1	90 1	
Solder	rability	≥ 95% of each terminal should be covered with fresh solder	Dip device in eutection for 5.0 ± 0.0	
	Appearance	No defects, <25% leaching of either end terminal		
	Capacitance	≤ ±20%		
	Variation	_ 12070	Dip device in eutectic	solder at 260°C for 60
Resistance to Solder Heat	Dissipation Factor	Meets Initial Values (As Above)	seconds. Store at room hours before measurin	temperature for 24 \pm 2
Colder Fleat	Insulation Resistance	Meets Initial Values (As Above)	Tiodre bolore modedim	g olocilloai proportios.
	Dielectric Strength	Meets Initial Values (As Above)		
	Appearance	No visual defects	Step 1: -30°C ± 2°	30 ± 3 minutes
	Capacitance Variation	≤ ±20%	Step 2: Room Temp	≤3 minutes
Thermal Shock	Dissipation Factor	Meets Initial Values (As Above)	Step 3: +85°C ± 2°	30 ± 3 minutes
OHOCK	Insulation Resistance	Meets Initial Values (As Above)	Step 4: Room Temp	≤3 minutes
	Dielectric Strength	Meets Initial Values (As Above)	Repeat for 5 cycles ar 24 ±2 hours at room to	
	Appearance	No visual defects		
	Capacitance Variation	≤ ±30%	Charge device with to	et at 85°C ± 2°C
Load Life	Dissipation Factor	≤ Initial Value x 1.5 (See Above)	for 1000 hou	
	Insulation Resistance	≥ Initial Value x 0.1 (See Above)	Remove from test ch at room temperatu	re for 24 ± 2 hours
	Dielectric Strength	Meets Initial Values (As Above)	before m	easuring.
	Appearance	No visual defects	Store in a test chamb	er set at 85°C + 2°C/
	Capacitance Variation	≤ ±30%	85% ± 5% relative hu (+48, -0) with rate	midity for 1000 hours
Load Humidity	Dissipation Factor	≤ Initial Value x 1.5 (See above)	Remove from cham	
	Insulation Resistance	≥ Initial Value x 0.1 (See Above)	room temperature 24 ± 2 hours be	e and humidity for
	Dielectric Strength	Meets Initial Values (As Above)	21 ± 2110013 00	



Y5V Dielectric





PREFERRED SIZES ARE SHADED

			0								.			ш	l				1					
SIZE		0	201			0402				06	03			080)5			120	06			12	210	
Solderi		_	w Only			eflow Or					//Wave			Reflow/				Reflow					v/Wave	
Packag			Paper			All Pape					aper		Р	aper/Em			F		nbossed			Paper/E		d
(L) Length	MM (in.)	(0.024	± 0.03 ± 0.001)		(0.0	.00 ± 0.1 040 ± 0.0	004)			1.60 =				2.01 ± (0.079 ± 1.25 ±	0.008)			3.20 ± (0.126 ± 1.60 ±	(800.0			(0.126	± 0.20 ± 0.008) ± 0.20)
(W) Width	(in.)	(0.011	± 0.001)		(0.0	0.020 ± 0.0	004)			(0.032 -	± 0.006)			$(0.049 \pm$	0.008)			$(0.063 \pm$	0.008)				± 0.20 ± 0.008))
(t) Terminal	MM (in.)		± 0.05 ± 0.002)			0.25 ± 0.1 010 ± 0.0				0.35 =				0.50 ± (0.020 ±				0.50 ± (0.020 ±					± 0.25 ± 0.010)	
WVDC	. ,	6.3	10	6.3	10	16	25	50	10	16	25	50	10	16	25	50	10	16	25	50	10	16	25	50
	2200 2700	1000 pl A	1000 pF A																					
	3300 3900	A A	A A																					
	4700 5600	A	A	С	С	C	С	С												_			-W	*
	6800 8200	A A	A A	CCC	C	CC	C	CCC															للر	ŢT
Cap (µF)	0.010 0.012	A A	А	C	C	C	C C	C C	G G	G G	G G	G G	E E	E E	E E	E E						1		
	0.015	A		C	C	C	C	C	G	G	G	G	E	E	E	E								
	0.022	A		C	C	C	C	С	G G	G G	G G	G G	E	E	E	E								
	0.033 0.039 0.047	A A A		CCC	CCC	CCC	С		G G G	G G G	G G G	G G G	E E	E E E	E E E	E E E	J	J	J	J				
	0.056 0.068			C	C	C			G G	G G	G G	G G	E E	E E	E E	E E	J	J	J	J J				
	0.082			C	C	C			G G	G G	G G	G G	E	E	E	E	J	J	J	J	J	J	J	J
	0.12 0.15			C	C				G G	G G	G G		J	J	J	J	J	J	J	J	J	J	J	J
	0.18 0.22 0.27			C	C				G G G	G G G	G G		J	J	J J	J J M	J	J	J	J	J J	J	J	J
	0.33								G G	G G			J	J	M M	М	J	J	J	J	J J	J	J	٠ د د
	0.47 0.56 0.68								G G G	G G G			J	J J	N N N		J J	J	J	J	J	J	J	J
	0.82								G	G			M N	M	N N		J	J	J	J	J	J	J	J
	1.2												N N	N N			J M	J M	M		J J	J	J	M M
	1.8 2.2 2.7												N N N	N N			M M M	M M M	M M		J J M	J J M	J J M	
_	3.3 3.9 4.7												N N P				M P P	M P P			P P P	P P P	M N	
	5.6 6.8												P				Q Q				Q Q	Q Q	IN	
	8.2																Q Q				Q Q	Q Q	Х	
	12.0 15.0																				X			
	18.0 22.0 47.0 100.0																				X			
WVDC	;	6.3	10	6.3	10	16	25	50	10	16	25	50	10	16	25	50	10	16	25	50	10	16	25	50
SIZE		0	201			0402				06	03			80	05			12	:06			12	10	
Letter	Α		С	Е		G			K		M	N		Р		Q	Х		Υ		Z	BB		CC
Max.	0.33		0.56	0.71		0.86	0.9		1.02		1.27	1.4		1.52		.78	2.29		2.54		79	3.05		3.175
Thickness	(0.013)	(0)	.022)	(0.028 PAPE		0.034)	(0.0)	37)	(0.040) (0	.050)	(0.05	00)	(0.060)		070) EMBO	(0.09 SSED	0) [((0.100)	(0.1	110)	(0.120) (0).125)

Contact Factory for Multiples



Automotive MLCC





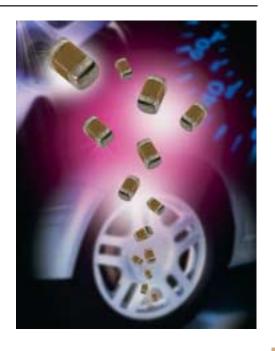
GENERAL DESCRIPTION

AVX Corporation has supported the Automotive Industry requirements for Multilayer Ceramic Capacitors consistently for more than 10 years. Products have been developed and tested specifically for automotive applications and all manufacturing facilities are QS9000 and VDA 6.4 approved.

As part of our sustained investment in capacity and state of the art technology, we are now transitioning from the established Pd/Ag electrode system to a Base Metal Electrode system (BME).

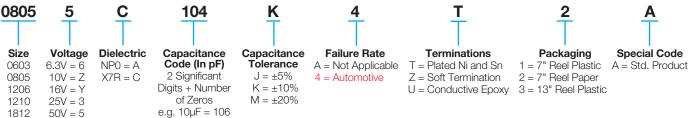
AVX is using AECQ200 as the qualification vehicle for this transition. A detailed qualification package is available on request and contains results on a range of part numbers including:

- X7R dielectric components containing BME electrode and copper terminations with a Ni/Sn plated overcoat.
- X7R dielectric components BME electrode and soft terminations with a Ni/Sn plated overcoat.
- NP0 dielectric components containing Pd/Ag electrode and silver termination with a Ni/Sn plated overcoat.



HOW TO ORDER

100V = 1200V = 2



COMMERCIAL VS AUTOMOTIVE MLCC PROCESS COMPARISON

	Commercial	Automotive
Administrative	Standard Part Numbers. No restriction on who purchases these parts.	Specific Automotive Part Number. Used to control supply of product to Automotive customers.
Design	Minimum ceramic thickness of 0.020"	Minimum Ceramic thickness of 0.029" (0.74mm) on all X7R product.
Dicing	Side & End Margins = 0.003" min	Side & End Margins = 0.004" min Cover Layers = 0.005" min
Lot Qualification (Destructive Physical Analysis - DPA)	As per EIA RS469	Increased sample plan – stricter criteria.
Visual/Cosmetic Quality	Standard process and inspection	100% inspection
Application Robustness	Standard sampling for accelerated wave solder on X7R dielectrics	Increased sampling for accelerated wave solder on X7R and NP0 followed by lot by lot reliability testing.

All Tests have Accept/Reject Criteria 0/1



Automotive MLCC

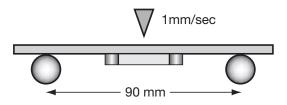
NP0/X7R Dielectric



SOFT TERMINATION FEATURES

a) Bend Test

The capacitor is soldered to the PC Board as shown:



Typical bend test results are shown below:

Style	Conventional Term	Soft Term
0603	>2mm	>5
0805	>2mm	>5
1206	>2mm	>5

b) Temperature Cycle testing "Soft Termination" has the ability to withstand at least 1000 cycles between -55°C and +125°C

ELECTRODE AND TERMINATION OPTIONS

NPO DIELECTRIC

NP0 Ag/Pd Electrode Nickel Barrier Termination PCB Application

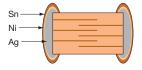


Figure 1 Termination Code T

X7R DIELECTRIC

X7R Dielectric PCB Application

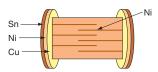


Figure 2 Termination Code T

X7R Nickel Electrode Soft Termination PCB Application

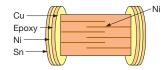


Figure 3 Termination Code Z

Conductive Epoxy Termination Hybrid Application

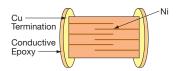


Figure 4 Termination Code U



NPO Automotive



Capacitance Range (Ni Barrier Termination)

		0603			0805			1206			12	10		18	12
	25V	50V	100V	25V	50V	100V	25V	50V	100V	25V	50V	100V	200V	50V	100V
R47															
R51 R56															
R62															
R68															
R75															
R82 R91															
1R0															
1R2															
1R5															
1R8 2R0												 	 	-	\vdash
2R2															
2R4															
2R7															
3R0 3R3															-
3R6															
3R9															
4R3															<u> </u>
4R7 5R1												<u> </u>	<u> </u>		\vdash
5R6															
6R2															
6R8															<u> </u>
7R5 8R2												 	 		-
9R1															
100															
120												ļ	ļ		
150 180															
220															
270															
330															
390 470												 	 	-	\vdash
510															
560															
680															
820 101															
121												 	 		\vdash
151															
181															
221 271															
331												-	-		\vdash
391															
471															
561 681															
821															
102															
122															
152 182					-										\vdash
222															\vdash
272															
332															
392 472				-		-							-		
562					 	-									
682															
822															
103	0517	501	40017	0517	F0\/	40011	05) (F0) /	40017	05) (F6) /	40017	00017	5017	400
	25V	50V	100V	25V	50V	100V	25V	50V	100V	25V		100V	200V	50V	1000
	I	0603			0805		<u> </u>	1206			12	10		18	12





BME X7R Automotive



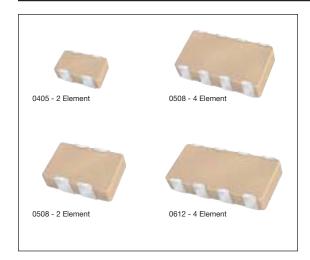
Capacitance Range (Ni Barrier Termination)

		(0603					0805					1206					1210					1812		
	16V	25V	50V	100V	200V	16V	25V	50V	100V	200V	16V	25V	50V	100V	200V	16V	25V	50V	100V	200V	16V	25V	50V	100V	200V
101																									
121																									
151																									\vdash
181 221				-		<u> </u>			-		_					_									\vdash
271											-					-		_							$\vdash \vdash$
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155	40)/	05):	50) (100);	0001	10)/	05) (50) (100);	000);	401/	051/	50)/	100);	000) :	40)/	05)/	50)/	100)	000)	40)/	051/	50) (100)	000);
	16V	25V	50V)603	100V	200V	16V	25V	50V 0805	100V	200V	16V	25V	50V 1206	100V	200V	16V	25V	50V 1210	100V	200V	16V	25V	50V 1812	100V	200V
			1003					0000					1200					1210					1012		

= Paper Tape
= Plastic Tape



Capacitor Array (IPC)



GENERAL DESCRIPTION

AVX is the market leader in the development and manufacture of capacitor arrays. The smallest array option available from AVX the 0405 2-element device, has been an enormous success in the Telecommunications market. The array family of products also includes the 0612 4-element device as well as 0508 2-element and 4-element series, all of which have received widespread acceptance in the marketplace.

AVX capacitor arrays are available in X5R, X7R and NPO (COG) ceramic dielectrics to cover a broad range of capacitance values. Voltage ratings from 6.3 Volts up to 100 Volts are offered.

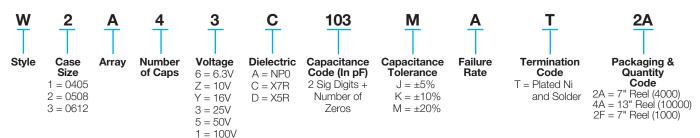
Key markets for capacitor arrays are Mobile and Cordless Phones, Digital Set Top Boxes, Computer Motherboards and Peripherals as well as Automotive applications, RF Modems, Networking Products etc.

AVAILABLE CAPACITANCE VALUES

Case	.,	NP0	/C0G	X5R/	X7R
Size	Voltage	Min. Cap	Max. Cap.	Min. Cap.	Мах. Сар.
	10v			124	474
	16v	100	471	221	104
0612	25v	100	471	221	104
4 element	50v	100	471	221	473
	100v	100	391	221	223
	10v			104	154
	16v	100	271	221	104
0508	25v	100	271	221	183
4 element	50v	100	271	221	183
	100v	100	221	221	472
	6.3v				105
	16v	100	471	221	104
0508	25v	100	471	221	333
2 element	50v	100	471	221	333
	100v	100	391	221	682
	10v			273	104
0405	16v	100	101	121	223
2 element	25v	100	101	121	682
	50v	100	101	121	682

= X5R

HOW TO ORDER





Capacitor Array (IPC)



BENEFITS OF USING CAPACITOR ARRAYS

AVX capacitor arrays offer designers the opportunity to lower placement costs, increase assembly line output through lower component count per board and to reduce real estate requirements.

Reduced Costs

Placement costs are greatly reduced by effectively placing one device instead of four or two. This results in increased throughput and translates into savings on machine time. Inventory levels are lowered and further savings are made on solder materials etc.

Space Saving

Space savings can be quite dramatic when compared to the use of discrete chip capacitors. As an example, the 0508 4-element array offers a space reduction of >40% vs. 4 x 0402 discrete capacitors and of >70% vs. 4 x 0603 discrete capacitors. (This calculation is dependent on the spacing of the discrete components.)

Increased Throughput

Assuming that there are 220 passive components placed in a mobile phone:

A reduction in the passive count to 200 (by replacing discrete components with arrays) results in an increase in throughput of approximately. 9%.

A reduction of 40 placements increases throughput by 18%.

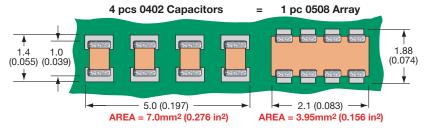
For high volume users of cap arrays using the very latest placement equipment capable of placing 10 components per second, the increase in throughput can be very significant and can have the overall effect of reducing the number of placement machines required to mount components:

If 120 million 2-element arrays or 40 million 4-element arrays were placed in a year, the requirement for placement equipment would be reduced by one machine.

During a 20Hr operational day a machine places 720K components. Over a working year of 167 days the machine can place approximately 120 million. If 2-element arrays are mounted instead of discrete components, then the number of placements is reduced by a factor of two and in the scenario where 120 million 2-element arrays are placed there is a saving of one pick and place machine.

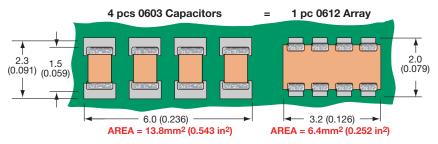
Smaller volume users can also benefit from replacing discrete components with arrays. The total number of placements is reduced thus creating spare capacity on placement machines. This in turn generates the opportunity to increase overall production output without further investment in new equipment.

W2A (0508) Capacitor Arrays



The 0508 4-element capacitor array gives a PCB space saving of over 40% vs four 0402 discretes and over 70% vs four 0603 discrete capacitors.

W3A (0612) Capacitor Arrays



The 0612 4-element capacitor array gives a PCB space saving of over 50% vs four 0603 discretes and over 70% vs four 0805 discrete capacitors.







GENERAL DESCRIPTION

A recent addition to the array product range is the Multi-Value Capacitor Array. These devices combine two different capacitance values in standard 'Cap Array' packages and are available with a maximum ratio between the two capacitance values of 100:1. The multi-value array is currently available in the 0405 and 0508 2-element styles.

Whereas to date AVX capacitor arrays have been suited to applications where multiple capacitors of the same value are used, the multi-value array introduces a new flexibility to the range. The multi-value array can replace discrete capacitors of different values and can be used for broadband decoupling applications. The 0508 x 2 element multi-value array would be particularly recommended in this application. Another application is filtering the 900/1800 or 1900MHz noise in mobile phones. The 0405 2-element, low capacitance value NPO, (COG) device would be suited to this application, in view of the space saving requirements of mobile phone manufacturers.

ADVANTAGES OF THE MULTI-VALUE CAPACITOR ARRAYS

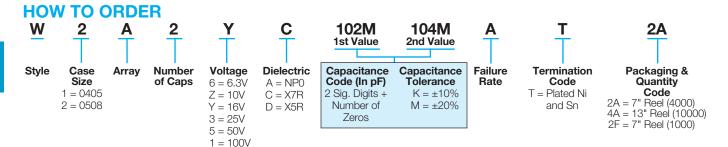
Enhanced Performance Due to Reduced Parasitic Inductance

When connected in parallel, not only do discrete capacitors of different values give the desired self-resonance, but an additional unwanted parallel resonance also results. This parallel resonance is induced between each capacitor's self-resonant frequencies and produces a peak in impedance response. For decoupling and bypassing applications this peak will result in a frequency band of reduced decoupling and in filtering applications reduced attenuation.

The multi-value capacitor array, combining capacitors in one unit, virtually eliminates the problematic parallel resonance, by minimizing parasitic inductance between the capacitors, thus enhancing the broadband decoupling/filtering performance of the part.

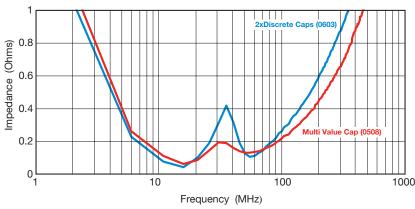
Reduced ESR

An advantage of connecting two capacitors in parallel is a significant reduction in ESR. However, as stated above, using discrete components brings with it the unwanted side effect of parallel resonance. The multi-value cap array is an excellent alternative as not only does it perform the same function as parallel capacitors but also it reduces the uncertainty of the frequency response.



IMPEDANCE vs FREQUENCY MULTI-VALUE ARRAY COMPARED TO DISCRETE CAPACITORS

10nF / 100nF Capacitor Impedance vs Frequency







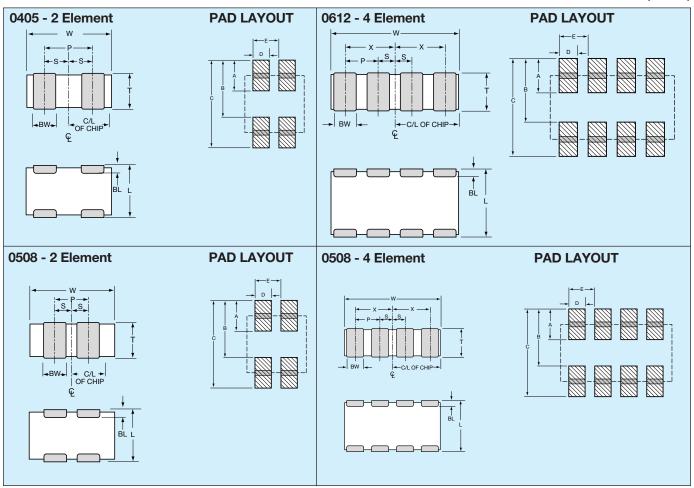
				1	IP			00	<u> </u>															7R	<u>/X</u>	5F							
SIZE		040	5		0	508	8			()508	3			061	2	SIZ		(405			05				_	508			C	612	<u>!</u>
Elements Soldering	Re	2 flow 0	nlv		Reflo	2 w/V	Vave			Refle	4 ow/M	/ave		Re	4 flow/\	Nave	# Elen	nents oldering	Refl	2 ow Or	nlv	F	2 Reflow/			F		4 //Wa\	re		Reflo	4 w/Wa	ave
Packaging	А	II Pap	er		All	Pap	er		P		/Emb		d	Pape	r/Eml	bossed		ckaging	All	Pape	r		All Pa	aper		Pap	er/E	mbos	sed	Pa		Embo	
ength MM (in.)		00 ± 0 39 ± 0			1.30 0.051			6)	(0 ± 0 1 ± 0)		60 ±	0.20 0.008)	Length	MM (in.)	1.0	0 ± 0.0			1.30 ± 051 ±		3)			± 0.18 ± 0.00		(($0 \pm 0.$ $3 \pm 0.$	
/idth MM	1.0	37 ± 0).15		2.10) ± ().15			2.10	0 ± C	.15		3.	20 ±	0.20	Width	MM	1.3	7 ± 0.	15	2	2.10 ±	0.15		- 2	2.10	± 0.1	5		3.20) ± 0.	.20
fax. MM	(0.08	54 ± 0 0.66		(0.083	3 ± (0.94		ó) <u> </u>	(3 ± 0 0.94	.006))	(0.1	26 ±	0.008) 5	Max.	(in.) MM	(0.05	1 ± 0.0 0.66)06)	(0.	083 ±		5)	(0.		± 0.00)6)	((3 ± 0. 1.35	008)
hickness (in.)		(0.026	3)		(0	0.037	7)			(0	0.037	,			(0.05	53)	Thickne	ss (in.)	(0).026)			(0.03	37)			(0.0	037)			(0	0.053)	
WVDC Cap 1.0	10	16 2	5 50	6.3	16	25	50	100	10	16	25	50	100	16	25	50 100	Cap	NDC 100	10 1	6 25	50	6.3 1	6 25	50	100	10 1	6 2	5 50	100	10	16	25	50
(pF) 1.2																	(pF)	120															
1.5		+													+			150 180		+		+	+			+	+					+	+
2.2 2.7																		220 270															
3.3														H	+			330		+													Ħ
3.9 4.7																		390 470															
5.6																		560															
6.8 8.2																		680 820															
10																		1000															П
12 15																		1200 1500															
18 22																		1800 2200															
27																		2700															
33 39																		3300 3900															
47															_			4700		+			4									4	
56 68																		5600 6800															
82 100																	Cap 0.	8200		-			+										\Box
120																	Οάρ υ.	0.012															
150 180																		0.015					+		_								\dashv
220																		0.022															
270 330																		0.027		+			+										
390 470																		0.039 0.047															
560																		0.056															
680 820																		0.068 0.082															
1000																		0.10															T
1200 1500																		0.12 0.15															
1800 2200																		0.18 0.22															
2700																		0.27			Ш												
3300 3900																		0.33 0.47															
4700		\perp	_									_		\sqcup	\perp	_		0.56	_	_	Ш	\perp	\perp		_	_	\perp	\perp	_			\perp	\dashv
5600 6800																		0.68 0.82															
8200 Cap 0.010	\vdash	+	+	\vdash	\dashv							\dashv		$\vdash \vdash$	+			1.0	+	+	\vdash		+	+	_	+	+	+	\vdash	\vdash	-	+	+
(μF)																		1.5															
	\vdash	+		H	\dashv									\vdash	+	+		1.8	+	+	H	+	+	\Box	-	+	+	+		H		+	+
																		3.3 4.7															
	\vdash	+	+											\vdash	+			10	+	+	\Box	+	+	+		+	+	+		H		+	+
																		22 47															
																		100															





PART & PAD LAYOUT DIMENSIONS

millimeters (inches)



PART DIMENSIONS

0405 - 2 Element

L	W	Т	BW	BL	Р	S
1.00 ± 0.15 (0.039 ± 0.006)	=	0.66 MAX (0.026 MAX)	0.36 ± 0.10 (0.014 ± 0.004)	0.20 ± 0.10 (0.008 ± 0.004)		0.32 ± 0.10 (0.013 ± 0.004)

0508 - 2 Element

L	W	T	BW	BL	Р	S
	2.10 ± 0.15 (0.083 ± 0.006)	0.94 MAX (0.037 MAX)	0.43 ± 0.10 (0.017 ± 0.004)	0.33 ± 0.08 (0.013 ± 0.003)	1.00 REF (0.039 REF)	0.50 ± 0.10 (0.020 ± 0.004)

0508 - 4 Element

L	W	T	BW	BL	Р	X	S
1.30 ± 0.15	2.10 ± 0.15	0.94 MAX	0.25 ± 0.06	0.20 ± 0.08	0.50 REF	0.75 ± 0.10	0.25 ± 0.10
(0.051 ± 0.006)	(0.083 ± 0.006)	(0.037 MAX)	(0.010 ± 0.003)	(0.008 ± 0.003)	(0.020 REF)	(0.030 ± 0.004)	(0.010 ± 0.004)

0612 - 4 Element

L	W	T	BW	BL	Р	Х	S
1.60 ± 0.20 (0.063 ± 0.008)	3.20 ± 0.20 (0.126 ± 0.008)	1.35 MAX (0.053 MAX)	0.41 ± 0.10 (0.016 ± 0.004)			1.14 ± 0.10 (0.045 ± 0.004)	

PAD LAYOUT DIMENSIONS

0405 - 2 Element

Α	В	С	D	E
0.46	0.74	1.20	0.30	0.64
(0.018)	(0.029)	(0.047)	(0.012)	(0.025)

0508 - 2 Element

١	Α	В	С	D	Е
	0.68	1.32	2.00	0.46	1.00
	(0.027)	(0.052)	(0.079)	(0.018)	(0.039)

0508 - 4 Element

Α	В	С	D	E
0.56	1.32	1.88	0.30	0.50
(0.022)	(0.052)	(0.074)	(0.012)	(0.020)

0612 - 4 Element

Α	В	С	D	Е
0.89	1.65	2.54	0.46	0.79
(0.035)	(0.065)	(0.100)	(0.018)	(0.031)





Introduction

As switching speeds increase and pulse rise times decrease the need to reduce inductance becomes a serious limitation for improved system performance. Even the decoupling capacitors, that act as a local energy source, can generate unacceptable voltage spikes: V = L (di/dt). Thus, in high speed circuits, where di/dt can be quite large, the size of the voltage spike can only be reduced by reducing L.

Figure 1 displays the evolution of ceramic capacitor toward lower inductance designs over the last few years. AVX has been at the forefront in the design and manufacture of these newer more effective capacitors.

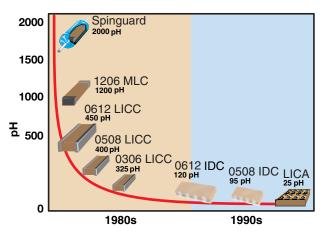


Figure 1. The evolution of Low Inductance Capacitors at AVX (values given for a 100 nF capacitor of each style)

LOW INDUCTANCE CHIP CAPACITORS

The total inductance of a chip capacitor is determined both by its length to width ratio and by the mutual inductance coupling between its electrodes. Thus a 1210 chip size has lower inductance than a 1206 chip. This design improvement is the basis of AVX's low inductance chip capacitors, LI Caps, where the electrodes are terminated on the long side of the chip instead of the short side. The 1206 becomes an 0612 as demonstrated in Figure 2. In the same manner, an 0805 becomes an 0508 and 0603 becomes an 0306. This results in a reduction in inductance from around 1200 pH for conventional MLC chips to below 400 pH for Low Inductance Chip Capacitors. Standard designs and performance of these LI Caps are given on pages 33 and 34.

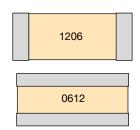
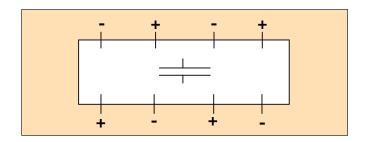


Figure 2. Change in aspect ratio: 1206 vs. 0612

INTERDIGITATED CAPACITORS

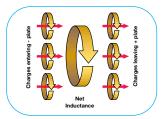
Multiple terminations of a capacitor will also help in reducing the parasitic inductance of the device. The IDC is such a device. By terminating one capacitor with 8 connections the ESL can be reduced even further. The measured inductance of the 0612 IDC is 120 pH, while the 0508 comes in around 95 pH. These FR4 mountable devices allow for even higher clock speeds in a digital decoupling scheme. Design and product offerings are shown on pages 35 and 36.



LOW INDUCTANCE CHIP ARRAYS (LICA®)

Further reduction in inductance can be achieved by designing alternative current paths to minimize the mutual inductance factor of the electrodes (Figure 3). This is achieved by AVX's LICA® product which was the result of a joint development between AVX and IBM. As shown in Figure 4, the charging current flowing out of the positive plate returns in the opposite direction along adjacent negative plates. This minimizes the mutual inductance.

The very low inductance of the LICA capacitor stems from the short aspect ratio of the electrodes, the arrangement of the tabs so as to cancel inductance, and the vertical aspect of the electrodes to the mounting surface.



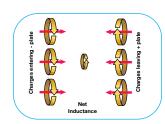


Figure 3. Net Inductance from design. In the standard Multilayer capacitor, the charge currents entering and leaving the capacitor create complementary flux fields, so the net inductance is greater. On the right, however, if the design permits the currents to be opposed, there is a net cancellation, and the inductance is much lower.







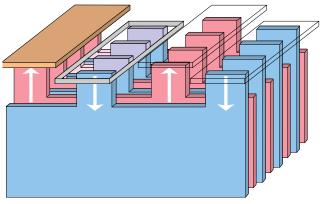


Figure 4. LICA's Electrode/Termination Construction.

The current path is minimized – this reduces self-inductance.

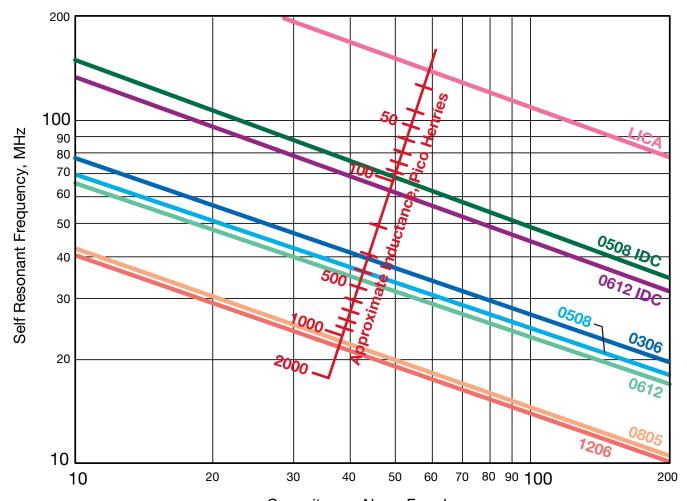
Current flowing out of the positive plate, returns in the opposite direction along the adjacent negative plate – this reduces the mutual inductance.

Also the effective current path length is minimized because the current does not have to travel the entire length of both electrodes to complete the circuit. This reduces the self inductance of the electrodes. The self inductance is also minimized by the fact that the charging current is supplied by both sets of terminals reducing the path length even further!

The inductance of this arrangement is less than 50 pH, causing the self-resonance to be above 100 MHz for the same popular 100 nF capacitance. Parts available in the LICA design are shown on pages 37 and 38.

Figure 5 compares the self resonant frequencies of various capacitor designs versus capacitance values. The approximate inductance of each style is also shown.

Active development continues on low inductance capacitors. C4 termination with low temperature solder is now available for plastic packages. Consult AVX for details.



Capacitance, Nano-Farads
Self Resonant Frequencies vs. Capacitance and Capacitor Design

Figure 5



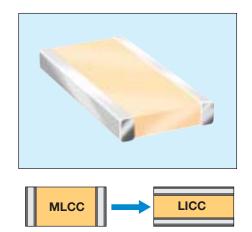


0612/0508/0306 LICC (Low Inductance Chip Capacitors)

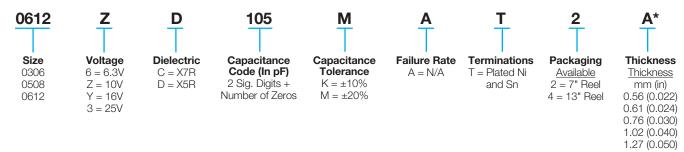
GENERAL DESCRIPTION

The total inductance of a chip capacitor is determined both by its length to width ratio and by the mutual inductance coupling between its electrodes

Thus a 1210 chip size has a lower inductance than a 1206 chip. This design improvement is the basis of AVX's Low Inductance Chip Capacitors (LICC), where the electrodes are terminated on the long side of the chip instead of the short side. The 1206 becomes an 0612, in the same manner, an 0805 becomes an 0508, an 0603 becomes an 0306. This results in a reduction in inductance from the 1nH range found in normal chip capacitors to less than 0.4nH for LICCs. Their low profile is also ideal for surface mounting (both on the PCB and on IC package) or inside cavity mounting on the IC itself.



HOW TO ORDER



PERFORMANCE CHARACTERISTICS

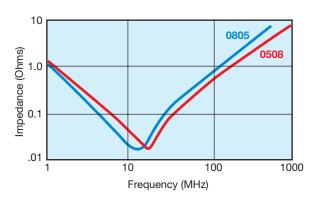
Capacitance Tolerances	$K = \pm 10\%$; $M = \pm 20\%$
Operation	$X7R = -55^{\circ}C \text{ to } +125^{\circ}C;$
Temperature Range	X5R = -55°C to $+85$ °C
Temperature Coefficient	±15% (0VDC)
Voltage Ratings	6.3, 10, 16, 25 VDC
Dissipation Factor	6.3V = 6.5% max; 10V = 5.0% max; 16V = 3.5% max; 25V = 3.0% max
Insulation Resistance (@+25°C, RVDC)	100,000M Ω min, or 1,000M Ω per μF min.,whichever is less

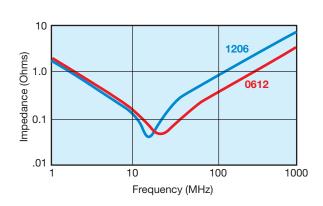
TYPICAL INDUCTANCE

Package Style	Measured Inductance (pH)
1206 MLCC	1200
0612 LICC	450
0508 LICC	400
0306 LICC	325

*Note: See Range Chart for Codes

TYPICAL IMPEDANCE CHARACTERISTICS









0612/0508/0306 LICC (Low Inductance Chip Capacitors)

SIZ	SIZE		06		05	08			061	2	
Length	MM (in.)	M 0.81 ± 0.15		,	1.27 ± 0.25 (0.050 ± 0.010)		1.60 ± 0.25 (0.063 ± 0.010)				
Width (in.) (0.032 ± 0.006) Width (in.) (0.063 ± 0.006)		(0.050 ± 0.010) 2.00 ± 0.25 (0.080 ± 0.010)				3.20 ± 0.25 (0.126 ± 0.010)					
W	VDC	10	16	6.3	10	16	25	6.3	10	16	25
	P (uF) hickness										
0.	010										
0.	.015										
0.	022										
0.	047										
0.	068										
0	1.10										
0	1.15										
0	1.22										
0	1.47										
0	1.68										
-	1.0										
-	1.5										
-	2.2										
	3.3										

Consult factory for additional requirements

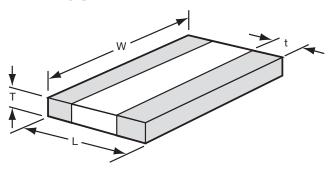


	mm (in.)		
0306 Code Thickness			

	mm (in.)			
	0508			
Code	Thickness			
S	0.56 (0.022)			
V	0.76 (0.030)			
Α	1.02 (0.040)			

	mm (in.)
	0612
Code	Thickness
S	0.56 (0.022)
V	0.76 (0.030)
W	1.02 (0.040)
Α	1.27 (0.050)

PHYSICAL DIMENSIONS AND PAD LAYOUT



PHYSICAL CHIP DIMENSIONS

mm (in)

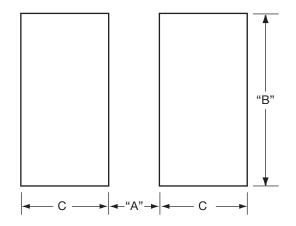
	L	W	t
0612	1.60 ± 0.25	3.20 ± 0.25	0.13 min.
	(0.063 ± 0.010)	(0.126 ± 0.010)	(0.005 min.)
0508	1.27 ± 0.25	2.00 ± 0.25	0.13 min.
	(0.050 ± 0.010)	(0.080 ± 0.010)	(0.005 min.)
0306	0.81 ± 0.15	1.60 ± 0.15	0.13 min.
	(0.032 ± 0.006)	(0.063 ± 0.006)	(0.005 min.)

T - See Range Chart for Thickness and Codes

PAD LAYOUT DIMENSIONS

mm (in)

			,
	A B		С
0612	0.76 (0.030)	3.05 (0.120)	.635 (0.025)
0508	0.51 (0.020)	2.03 (0.080)	0.51 (0.020)
0306	0.31 (0.012)	1.52 (0.060)	0.51 (0.020)



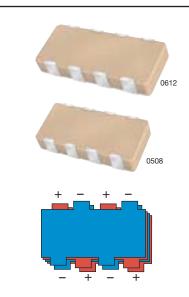


0612/0508 IDC (InterDigitated Capacitors)

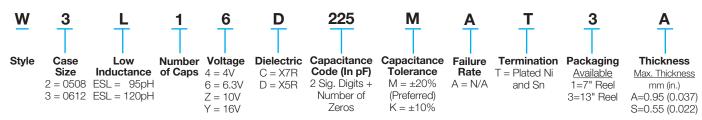


GENERAL DESCRIPTION

- Very low equivalent series inductance (ESL), surface mountable, high speed decoupling capacitor in 0612 and 0508 case size.
- Measured inductances of 120 pH (for 0612) and 95 pH (for 0508) are the lowest in the FR4 mountable device family.
- Opposing current flow creates opposing magnetic fields. This
 causes the fields to cancel, effectively reducing the equivalent
 series inductance.
- Perfect solution for decoupling high speed microprocessors by allowing the engineers to lower the power delivery inductance of the entire system through the use of eight vias.
- Overall reduction in decoupling components due to very low series inductance and high capacitance.



HOW TO ORDER



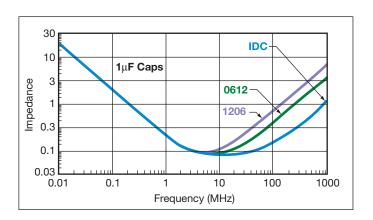
PERFORMANCE CHARACTERISTICS

Capacitance Tolerance	±20% Preferred (10% Available)
Operation	$X7R = -55^{\circ}C \text{ to } +125^{\circ}C;$
Temperature Range	X5R = -55°C to $+85$ °C
Temperature Coefficient	±15% (0VDC)
Voltage Ratings	4, 6.3, 10, 16 VDC
Dissipation Factor	4V, 6.3V = 6.5% max;
	10V = 5.0% max;
	16V = 3.5% max
Insulation Resistance	100,000M Ω min, or 1,000M Ω per
(@+25°C, RVDC)	μF min.,whichever is less

Dielectric Strength	No problems observed after 2.5 x RVDC for 5 seconds at 50mA max current
CTE (ppm/C)	12.0
Thermal Conductivity	4-5W/M K
Terminations Available	Plated Nickel and Solder
Max. Thickness	0.037" (0.95mm)

TYPICAL ESL AND IMPEDANCE

Package Style	Measured Inductance (pH)
1206 MLCC	1200
0612 LICC	450
0612 IDC	120
0508 IDC	95





Low Inductance Capacitors



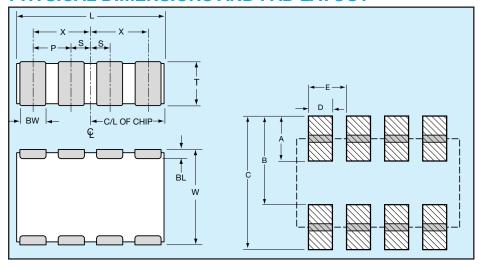
0612/0508 IDC (InterDigitated Capacitors)

SIZE			Thin	0508		0508			Thin	0612			06	12			
Length	MM			± 0.20				± 0.20			3.20 ±					± 0.20	
20119411	(in.)	((0.080 ± 0.008)			(0.080 ± 0.008)			(0.126 ± 0.008))	(0.126 ± 0.008)				
Width	MM		1.27 :	± 0.20			1.27	± 0.20			1.60 ±	0.20			1.60	± 0.20	
VVIGITI	(in.)	(0.050	± 0.008	5)		(0.050)	± 0.00	8)	(0.063 ±	0.008)		(0.063)	± 0.00	8)
Terminal	MM		0.508	3 REF			0.50	8 REF			0.76	REF			0.7	6 REF	
Pitch	(in.)		0.020	REF			0.02	0 REF			0.030	REF			0.03	30 REF	
Thickness	MM		0.55	MAX.			0.95	MAX.			0.55	MAX.			0.95	MAX.	
Trickness	(in.)		(0.022) MAX.			(0.03)	7) MAX			(0.022)	MAX.			(0.03)	7) MAX	
Inductance	(pH)		9)5				95			12	20			-	120	
WVDC		4	6.3	10	16	4	6.3	10	16	4	6.3	10	16	4	6.3	10	16
CA	P (uF)																
and Thick	kness																
	0.047																
<u> </u>	0.041																
	0.068																
	0.10																
	0.22									_							
	0.33																
	0.00									_							
	0.47																
	0.68																
	1.0																
	1.0																
	1.5																
	2.2																
	3.3																
	ა.ა														l	l	

Consult factory for additional requirements



PHYSICAL DIMENSIONS AND PAD LAYOUT



PHYSICAL CHIP DIMENSIONS millimeters (inches)

0612

L	W	BW	BL	Р	Х	S
3.20 ± 0.20	1.60 ± 0.20		0.18 +0.25 -0.08	0.76 REF	1.14 ± 0.10	0.38 ± 0.10
(0.126 ± 0.008)	(0.063 ± 0.008)	(0.016 ± 0.004)	(0.007+0.010)	(0.030 REF)	(0.045 ± 0.004)	(0.015 ± 0.004)

0508

L	W	BW	BL	Р	X	S
2.03±0.20 (0.080±0.008)	1.27±0.20 (0.050±0.008)	0.254±0.10 (0.010±0.004)	0.18 ^{+0.25} _{-0.08} (0.007 ^{+0.010})	0.508 REF (0.020 REF)	0.76±0.10 (0.030±0.004)	0.254±0.10 (0.010±.0.004)

PAD LAYOUT DIMENSIONS

0612

Α	В	ВС		Е	
0.89	1.65	2.54	0.46	0.76	
(0.035)	(0.065)	(0.100)	(0.018)	(0.030)	

0508

Α	В	ВС		E	
0.64	1.27	1.91	0.28	0.51	
(0.025)	(0.050)	(0.075)	(0.011)	(0.020)	



Low Inductance Capacitors



LICA® (Low Inductance Decoupling Capacitor Arrays)



LICA® arrays utilize up to four separate capacitor sections in one ceramic body (see Configurations and Capacitance Options). These designs exhibit a number of technical advancements:

Low Inductance features-

Low resistance platinum electrodes in a low aspect ratio pattern Double electrode pickup and perpendicular current paths C4 "flip-chip" technology for minimal interconnect inductance

HOW TO ORDER

LICA	3	Т	102	M	3	F	С	4	Α	Α
	\top	T	$\overline{}$	T	T	T	T	T	T	T
Style	Voltage	Dielectric	Cap/Section	Capacitance	Height	Termination	Reel Packaging	# of	Inspection	Code
&	5V = 9	D = X5R	(EIA Code)	Tolerance	Code	F = C4 Solder	M = 7" Reel	Caps/Part	Code	Face
Size	25V = 3	T = T55T	102 = 1000 pF	$M = \pm 20\%$	6 = 0.500mm	Balls- 97Pb/3Sn	R = 13" Reel	1 = one	A = Standard	A = Bar
	50V = 5	S = High K	103 = 10 nF	P = GMV	3 = 0.650mm	P = Cr-Cu-Au	6 = 2"x2" Waffle Pack	2 = two	B = Established	B = No Bar
		T55T	104 = 100 nF		1 = 0.875mm	N = Cr-Ni-Au	8 = 2"x2" Black Waffle	4 = four	Reliability	C = Dot, S55S
					5 = 1.100mm	X = None	Pack		Testing	Dielectrics
					7 = 1.600mm		7 = 2"x2" Waffle Pack			
TADIE	4						w/ termination			

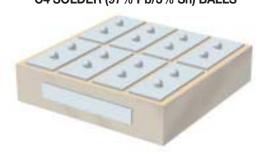
TABLE 1

Typical Parameters	T55T	Units
Capacitance, 25°C	Co	Nanofarads
Capacitance, 55°C	1.4 x Co	Nanofarads
Capacitance, 85°C	Co	Nanofarads
Dissipation Factor 25°	12	Percent
DC Resistance	0.2	Ohms
IR (Minimum @25°)	2.0	Megaohms
Dielectric Breakdown, Min	500	Volts
Thermal Coefficient of Expansion	8.5	ppm/°C 25-100°
Inductance: (Design Dependent)	15 to 120	Pico-Henries
Frequency of Operation	DC to 5 Gigahertz	
Ambient Temp Range	-55° to 125°C	

TERMINATION OPTIONS

facing up A = 2"x2" Black Waffle Pack w/ termination facing up C = 4"x4" Waffle Pack w/ clear lid

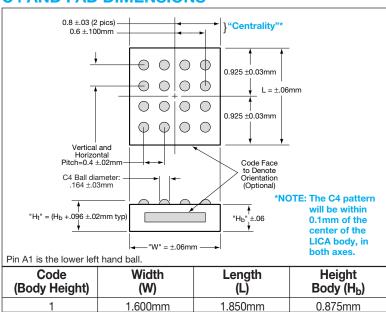
C4 SOLDER (97% Pb/3% Sn) BALLS



TERMINATION OPTION P OR N



C4 AND PAD DIMENSIONS



1.850mm

1.850mm

1.850mm

1.850mm

1.600mm

1.600mm

1.600mm

1.600mm

1.600mm

5

6

7



0.875mm

0.650mm

1.100mm

0.500mm

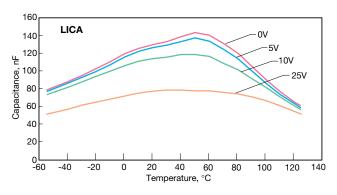
1.600mm

Low Inductance Capacitors

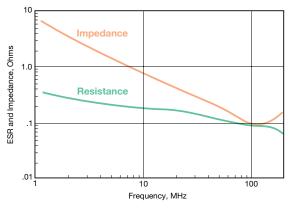


LICA® (Low Inductance Decoupling Capacitor Arrays)

LICA® TYPICAL PERFORMANCE CURVES



Effect of Bias Voltage and Temperature on a 130 nF LICA® (T55T)

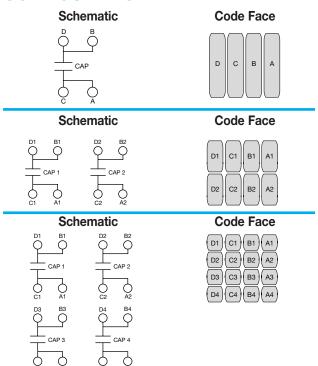


Impedance vs. Frequency

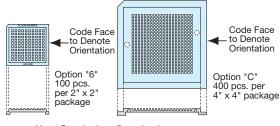
LICA VALID PART NUMBER LIST

Part Number	Voltage	Thickness (mm)	Capacitors per Package
LICA3T183M3FC4AA	25	0.650	4
LICA3T143P3FC4AA	25	0.650	4
LICA3T134M1FC1AA	25	0.875	1
LICA3T104P1FC1AA	25	0.875	1
LICA3T253M1FC4AA	25	0.875	4
LICA3T203P1FC4AA	25	0.875	4
LICA3T204M5FC1AA	25	1.100	1
LICA3T164P5FC1AA	25	1.100	1
LICA3T304M7FC1AB	25	1.600	1
LICA3T244P7FC1AB	25	1.600	1
LICA5T802M1FC4AB	50	0.875	4
LICA5T602P1FC4AB	50	0.875	4
Extended Range			
LICA9D683M6FC4AB	5	0.500	4
LICA3T104M3FC1A	25	0.650	1
LICA3T803P3FC1A	25	0.650	1
LICA3T503M3FC2A	25	0.650	2
LICA3T403P3FC2A	25	0.650	2
LICA3S213M3FC4A	25	0.650	4

CONFIGURATION



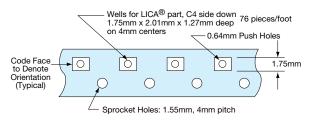
WAFFLE PACK OPTIONS FOR LICA®



Note: Standard configuration is Termination side down

LICA® PACKAGING SCHEME "M" AND "R"

8mm conductive plastic tape on reel: "M"=7" reel max. qty. 3,000, "R"=13" reel max. qty. 8,000

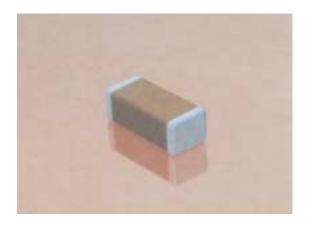




High Voltage Chips

For 500V to 5000V Applications





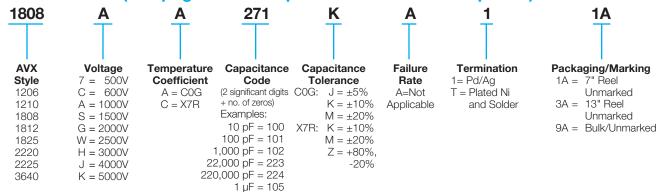
High value, low leakage and small size are difficult parameters to obtain in capacitors for high voltage systems. AVX special high voltage MLC chips capacitors meet these performance characteristics and are designed for applications such as snubbers in high frequency power converters, resonators in SMPS, and high voltage coupling/DC blocking. These high voltage chip designs exhibit low ESRs at high frequencies.

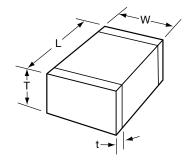
Larger physical sizes than normally encountered chips are used to make high voltage chips. These larger sizes require that special precautions be taken in applying these chips in surface mount assemblies. This is due to differences in the coefficient of thermal expansion (CTE) between the substrate materials and chip capacitors. Apply heat at less than 4°C per second during the preheat. Maximum preheat temperature must be within 50°C of the soldering temperature. The solder temperature should not exceed 230°C. Chips 1808 and larger to use reflow soldering only.

Capacitors with X7R Dielectrics are not intended for AC line filtering applications.

Contact plant for recommendations. Capacitors may require protective surface coating to prevent external arcing.

PART NUMBER (see page 2 for complete information and options)





DIMENSIONS

millimeters (inches)

SIZE		1206	1210	1808*	1812*	1825*	2220*	2225*	3640*
(L) Length		3.20 ± 0.2 (0.126 ± 0.008)	3.20 ± 0.2 (0.126 ± 0.008)	4.57 ± 0.25 (0.180 ± 0.010)	4.50 ± 0.3 (0.177 ± 0.012)	4.50 ± 0.3 (0.177 ± 0.012)	5.7 ± 0.4 (0.224 ± 0.016)	5.72 ± 0.25 (0.225 ± 0.010)	9.14 ± 0.25 (0.360 ± 0.010)
(W) Width		1.60 ± 0.2 (0.063 ± 0.008)	2.50 ± 0.2 (0.098 ± 0.008)	2.03 ± 0.25 (0.080 ± 0.010)	3.20 ± 0.2 (0.126 ± 0.008)	6.40 ± 0.3 (0.252 ± 0.012)	5.0 ± 0.4 (0.197 ± 0.016)	6.35 ± 0.25 (0.250 ± 0.010)	10.2 ± 0.25 (0.400 ± 0.010)
(T) Thickness Max.		1.52 (0.060)	1.70 (0.067)	2.03 (0.080)	2.54 (0.100)	2.54 (0.100)	3.3 (0.130)	2.54 (0.100)	2.54 (0.100)
(t) terminal	min. max.	0.25 (0.010) 0.75 (0.030)	0.25 (0.010) 0.75 (0.030)	0.25 (0.010) 1.02 (0.040)	0.25 (0.010) 1.02 (0.040)	0.25 (0.010) 1.02 (0.040)	0.25 (0.010) 1.02 (0.040)	0.25 (0.010) 1.02 (0.040)	0.76 (0.030) 1.52 (0.060)

^{*}Reflow Soldering Only



High Voltage Chips

For 500V to 5000V Applications



C0G Dielectric

PERFORMANCE CHARACTERISTICS

Capacitance Range	10 pF to 0.047 μF (25°C, 1.0 ±0.2 Vrms at 1kHz, for ≤ 1000 pF use 1 MHz)
Capacitance Tolerances	±5%, ±10%, ±20%
Dissipation Factor	0.1% max. (+25°C, 1.0 ±0.2 Vrms, 1kHz, for ≤ 1000 pF use 1 MHz)
Operating Temperature Range	-55°C to +125°C
Temperature Characteristic	0 ±30 ppm/°C (0 VDC)
Voltage Ratings	500, 600, 1000, 1500, 2000, 2500, 3000, 4000 & 5000 VDC (+125°C)
Insulation Resistance (+25°C, at 500 VDC)	100K M Ω min. or 1000 M Ω - μ F min., whichever is less
Insulation Resistance (+125°C, at 500 VDC)	10K M Ω min. or 100 M Ω - μ F min., whichever is less
Dielectric Strength	500V, 150% rated voltage for 5 seconds at 50 mA max. current ≥ 600V, 120% rated voltage for 5 seconds at 50 mA max. current

HIGH VOLTAGE COG CAPACITANCE VALUES

VOLT	AGE	1206	1210	1808	1812	1825	2220	2225	3640
500	min.	_		_	_	_	_		
300	max.	680 pF	1500 pF	3300 pF	5600 pF	0.012 µF	_	0.018 µF	_
600	min.	100 pF	100 pF	100 pF	100 pF	1000 pF	1000 pF	1000 pF	1000 pF
000	max.	680 pF	1500 pF	2700 pF	5600 pF	0.012 µF	0.012 μF	0.015 µF	0.047 µF
1000	min.	10 pF	100 pF	100 pF	100 pF	100 pF	1000 pF	1000 pF	1000 pF
1000	max.	470 pF	820 pF	1500 pF	2700 pF	6800 pF	0.010 µF	0.010 µF	0.018 µF
1500	min.	10 pF	100 pF	10 pF	10 pF	100 pF	1000 pF	1000 pF	100 pF
1300	max.	150 pF	330 pF	470 pF	1000 pF	2700 pF	2700 pF	3300 pF	8200 pF
2000	min.	10 pF	10 pF	10 pF	10 pF	100 pF	1000 pF	1000 pF	100 pF
2000	max.	68 pF	150 pF	270 pF	680 pF	1800 pF	2200 pF	2200 pF	5600 pF
2500	min.	_		10 pF	10 pF	10 pF	100 pF	100 pF	100 pF
2300	max.	_	-	150 pF	390 pF	1000 pF	1000 pF	1200 pF	3900 pF
3000	min.	_		10 pF	10 pF	10 pF	10 pF	10 pF	100 pF
3000	max.	_		100 pF	330 pF	680 pF	680 pF	820 pF	2200 pF
4000	min.	_	_	10 pF	10 pF	10 pF	10 pF	10 pF	100 pF
4000	max.	_		39 pF	100 pF	220 pF	220 pF	330 pF	1000 pF
5000	min.	_	_	_	_	_	_	_	10 pF
3000	max.	_	_	_	_	_	_	_	680 pF

X7R Dielectric

PERFORMANCE CHARACTERISTICS

Capacitance Range	10 pF to 0.56 μF (25°C, 1.0 ±0.2 Vrms at 1kHz)
Capacitance Tolerances	±10%; ±20%; +80%, -20%
Dissipation Factor	2.5% max. (+25°C, 1.0 ±0.2 Vrms, 1kHz)
Operating Temperature Range	-55°C to +125°C
Temperature Characteristic	±15% (0 VDC)
Voltage Ratings	500,600, 1000, 1500, 2000, 2500, 3000, 4000 & 5000 VDC (+125°C)
Insulation Resistance (+25°C, at 500 VDC)	100K M Ω min. or 1000 M Ω - μ F min., whichever is less
Insulation Resistance (+125°C, at 500 VDC)	10K M Ω min. or 100 M Ω - μ F min., whichever is less
Dielectric Strength	500V, 150% rated voltage for 5 seconds at 50 mA max. current
-	≥ 600V, 120% rated voltage for 5 seconds at 50 mA max. current

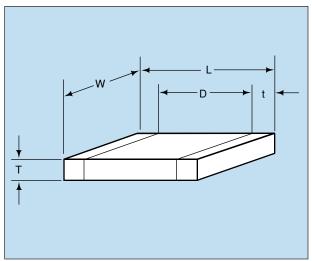
HIGH VOLTAGE X7R MAXIMUM CAPACITANCE VALUES

VOLT	AGE	1206	1210	1808	1812	1825	2220	2225	3640
500	min. max.	— 0.010 µF	— 0.027 μF	_	— 0.056 µF		_	_	_
600	min. max.	1000 pF 0.015 µF	1000 pF 0.027 μF	.01 μF 0.033 μF	.01 µF 0.068 µF	.01 μF 0.15 μF	.01 μF 0.15 μF	.01 μF 0.22 μF	.01 μF 0.56 μF
1000	min. max.	1000 pF 4700 pF	1000 pF 0.010 μF	1000 pF 0.015 µF	1000 pF 0.027 µF	1000 pF 0.068 µF	.01 µF 0.068 µF	.01 µF 0.082 µF	.01 μF 0.22 μF
1500	min. max.	100 pF 1200 pF	100 pF 2700 pF	100 pF 3900 pF	100 pF 8200 pF	1000 pF 0.018 µF	1000 pF 0.022 µF	1000 pF 0.027 µF	.01 μF 0.068 μF
2000	min. max.	10 pF 470 pF	100 pF 1000 pF	100 pF 1800 pF	100 pF 4700 pF	100 pF 8200 pF	1000 pF 0.010 µF	1000 pF 0.012 µF	1000 pF 0.027 μF
2500	min. max.		_	10 pF 1200 pF	10 pF 2200 pF	100 pF 5600 pF	1000 pF 6800 pF	1000 pF 8200 pF	1000 pF 0.022 μF
3000	min. max.	1 1		10 pF 560 pF	10 pF 1200 pF	100 pF 2700 pF	1000 pF 3300pF	1000 pF 4700 pF	1000 pF 0.018 µF
4000	min. max.								100 pF 6800 pF
5000	min. max.	_ _		_ _		_ _			100 pF 3300 pF

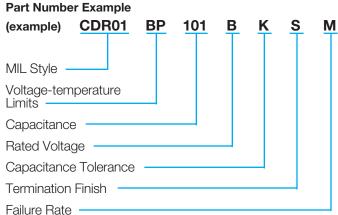


Part Number Example CDR01 thru CDR06





MILITARY DESIGNATION PER MIL-PRF-55681



MIL Style: CDR01, CDR02, CDR03, CDR04, CDR05, CDR06

Voltage Temperature Limits:

BP = 0 ± 30 ppm/°C without voltage; 0 ± 30 ppm/°C with rated voltage from -55°C to +125°C

BX = $\pm 15\%$ without voltage; +15-25% with rated voltage from -55°C to +125°C

Capacitance: Two digit figures followed by multiplier (number of zeros to be added) e.g., 101 = 100 pF

Rated Voltage: A = 50V, B = 100V

Capacitance Tolerance: $J \pm 5\%$, $K \pm 10\%$, $M \pm 20\%$

Termination Finish:

M = Palladium Silver N = Silver Nickel Gold S = Solder-coated U = Base Metallization/Barrier Metal/Solder Coated* W = Base Metallization/Barrier Metal/Tipped (Tip or Tip/

 Base Metallization/Barrier
 Metal/Tinned (Tin or Tin/ Lead Alloy)

*Solder shall have a melting point of 200°C or less.

Failure Rate Level: M = 1.0%, P = .1%, R = .01%, S = .001%

Packaging: Bulk is standard packaging. Tape and reel per RS481 is available upon request.

CROSS REFERENCE: AVX/MIL-PRF-55681/CDR01 THRU CDR06*

Per AVX		Longth (L)	Longth (L) Midth (M)		Thickness (T) D		Termination Band (t)		
MIL-PRF-55681	Style	Length (L)	Width (W)	Max.	Min.	Max.	Min.	Max.	Min.
CDR01	0805	.080 ± .015	$.050 \pm .015$.055	.020	_	.030	_	.010
CDR02	1805	.180 ± .015	$.050 \pm .015$.055	.020	_	_	.030	.010
CDR03	1808	.180 ± .015	$.080 \pm .018$.080	.020	_	_	.030	.010
CDR04	1812	.180 ± .015	.125 ± .015	.080	.020	_	_	.030	.010
CDR05	1825	.180 ^{+.020} 015	.250 +.020 015	.080	.020	_	_	.030	.010
CDR06	2225	.225 ± .020	.250 ± .020	.080	.020	_	_	.030	.010

*For CDR11, 12, 13, and 14 see AVX Microwave Chip Capacitor Catalog



MIL-PRF-55681/Chips Military Part Number Identification CDR01 thru CDR06



CDR01 thru CDR06 to MIL-PRF-55681

Military Type Designation	Capacitance in pF	Capacitance tolerance	Rated temperature and voltage- temperature limits	WVDC
AVX Style 08	805/CDR01			
CDR01BP100B CDR01BP150B CDR01BP150B CDR01BP20B CDR01BP270B CDR01BP300B CDR01BP390B CDR01BP470B CDR01BP560B CDR01BP680B CDR01BP680B CDR01BP820B	10 12 15 18 22 27 33 39 47 56 68	J,K J,K J,K J,K J,K J,K J,K J,K	BP BP BP BP BP BP BP BP BP	100 100 100 100 100 100 100 100 100 100
CDR01BP101B CDR01B121B CDR01B151B	100 120 150	J,K J,K J,K	BP BP,BX BP,BX	100 100 100 100
CDR01B181B	180	J,K	BP,BX	100
CDR01BX221B	220	K,M	BX	100
CDR01BX271B	270	K	BX	100
CDR01BX331B	330	K,M	BX	100
CDR01BX391B	390	K	BX	100
CDR01BX471B	470	K,M	BX	100
CDR01BX561B	560	K	BX	100
CDR01BX681B	680	K,M	BX	100
CDR01BX821B	820	K	BX	100
CDR01BX102B	1000	K,M	BX	100
CDR01BX122B	1200	K	BX	100
CDR01BX152B	1500	K,M	BX	100
CDR01BX182B	1800	K	BX	100
CDR01BX222B	2200	K,M	BX	100
CDR01BX272B	2700	K	BX	100
CDR01BX332B	3300	K,M	BX	100
CDR01BX392A	3900	K	BX	50
CDR01BX472A	4700	K,M	BX	50
AVX Style 18	805/CDR02			
CDR02BP221B	220	J,K	BP	100
CDR02BP271B	270	J	BP	100
CDR02BX392B	3900	K	BX	100
CDR02BX472B	4700	K,M	BX	100
CDR02BX562B	5600	K	BX	100
CDR02BX682B	6800	K,M	BX	100
CDR02BX822B	8200	K	BX	100
CDR02BX103B	10,000	K,M	BX	100
CDR02BX123A	12,000	K	BX	50
CDR02BX153A	15,000	K,M	BX	50
CDR02BX183A	18,000	K	BX	50
CDR02BX223A	22,000	K,M	BX	50

	22,000	K,M				
	- Add appropriate	failure rate				
	Add appropriate termination finish					
_	- Capacitance Tole	erance				

Military Type Designation	Capacitance in pF	Capacitance tolerance	Rated temperature and voltage-temperature limits	WVDC
AVX Style 18	808/CDR03			
CDR03BP331B CDR03BP391B CDR03BP471B CDR03BP561B CDR03BP681B CDR03BP821B	330 390 470 560 680 820	J,K J J,K J J,K	BP BP BP BP BP	100 100 100 100 100
CDR03BP102B CDR03BX123B CDR03BX153B CDR03BX183B	1000 12,000 15,000 18,000	J,K K K,M K	BP BX BX BX	100 100 100 100
CDR03BX223B CDR03BX273B CDR03BX333B CDR03BX393A CDR03BX473A	22,000 27,000 33,000 39,000 47,000	K,M K K,M K K,M	BX BX BX BX BX	100 100 100 50 50
CDR03BX563A CDR03BX683A	56,000 68,000	K K,M	BX BX	50 50
AVX Style 18	312/CDR04			
CDR04BP122B CDR04BP152B CDR04BP182B CDR04BP222B CDR04BP272B	1200 1500 1800 2200 2700	J J,K J J,K J	BP BP BP BP BP	100 100 100 100 100
CDR04BP332B CDR04BX393B CDR04BX473B CDR04BX563B CDR04BX823A	3300 39,000 47,000 56,000 82,000	J,K K K,M K	BP BX BX BX BX	100 100 100 100 50
CDR04BX104A CDR04BX124A CDR04BX154A CDR04BX184A	100,000 120,000 150,000 180,000	K,M K K,M K	BX BX BX BX	50 50 50 50
AVX Style 18	325/CDR05			
CDR05BP392B CDR05BP472B CDR05BP562B CDR05BX683B CDR05BX823B	3900 4700 5600 68,000 82,000	J,K J,K J,K K,M K	BP BP BP BX BX	100 100 100 100 100
CDR05BX104B CDR05BX124B CDR05BX154B CDR05BX224A CDR05BX274A	100,000 120,000 150,000 220,000 270,000	K,M K K,M K,M	BX BX BX BX	100 100 100 50 50
CDR05BX334A	330,000 225/CDR06	K,M	BX	50
AVX Style 22			DD	100
CDR06BP682B CDR06BP822B CDR06BP103B CDR06BX394A CDR06BX474A	6800 8200 10,000 390,000 470,000	J,K J,K J,K K K,M	BP BP BP BX BX	100 100 100 50 50

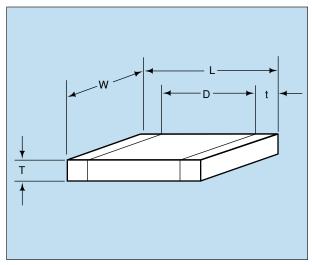
Add appropriate failure rate

Add appropriate termination finish

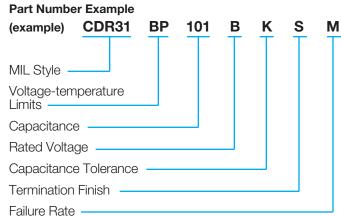


Part Number Example CDR31 thru CDR35





MILITARY DESIGNATION PER MIL-PRF-55681



MIL Style: CDR31, CDR32, CDR33, CDR34, CDR35

Voltage Temperature Limits:

BP = 0 ± 30 ppm/°C without voltage; 0 ± 30 ppm/°C with rated voltage from -55°C to +125°C

BX = $\pm 15\%$ without voltage; +15 –25% with rated voltage from -55°C to +125°C

Capacitance: Two digit figures followed by multiplier (number of zeros to be added) e.g., 101 = 100 pF

Rated Voltage: A = 50V, B = 100V

Capacitance Tolerance: C \pm .25 pF, D \pm .5 pF, F \pm 1% J \pm 5%, K \pm 10%, M \pm 20%

Termination Finish:

M = Palladium Silver N = Silver Nickel Gold S = Solder-coated U = Base Metallization/Barrier Metal/Solder Coated*
 W = Base Metallization/Barrier Metal/Tinned (Tin or Tin/ Lead Alloy)

*Solder shall have a melting point of 200°C or less.

Failure Rate Level: M = 1.0%, P = .1%, R = .01%, S = .001%

Packaging: Bulk is standard packaging. Tape and reel per RS481 is available upon request.

CROSS REFERENCE: AVX/MIL-PRF-55681/CDR31 THRU CDR35

Per MIL-PRF-55681 AVX		Length (L)	Width (W)	Thickness (T)	D	Terminatio	n Band (t)
(Metric Sizes)	Style	(mm)	(mm)	Max. (mm)	Min. (mm)	Max. (mm)	Min. (mm)
CDR31	0805	2.00	1.25	1.3	.50	.70	.30
CDR32	1206	3.20	1.60	1.3		.70	.30
CDR33	1210	3.20	2.50	1.5	_	.70	.30
CDR34	1812	4.50	3.20	1.5	_	.70	.30
CDR35	1825	4.50	6.40	1.5	_	.70	.30





Military Part Number Identification CDR31

CDR31 to MIL-PRF-55681/7

Military	Capacitance	Capacitance	Rated temperature	WVDC
Type Designation <u>1</u> /	in pF	tolerance	and voltage- temperature limits	
AVX Style 0	805/CDR31	(BP)		
CDR31BP1R0B	1.0	B,C	BP	100
CDR31BP1R1B	1.1	B,C	BP	100
CDR31BP1R2B	1.2	B,C	BP	100
CDR31BP1R3B	1.3	B,C	BP	100
CDR31BP1R5B	1.5	B,C	BP	100
CDR31BP1R6B	1.6	B,C	BP	100
CDR31BP1R8B	1.8	B,C	BP	100
CDR31BP2R0B	2.0	B,C	BP	100
CDR31BP2R2B	2.2	B,C	BP	100
CDR31BP2R4B	2.4	B,C	BP	100
CDR31BP2R7B	2.7	B,C,D	BP	100
CDR31BP3R0B	3.0	B,C,D	BP	100
CDR31BP3R3B	3.3	B,C,D	BP	100
CDR31BP3R6B	3.6	B,C,D	BP	100
CDR31BP3R9B	3.9	B,C,D	BP	100
CDR31BP4R3B	4.3	B,C,D	BP	100
CDR31BP4R7B	4.7	B,C,D	BP	100
CDR31BP5R1B	5.1	B,C,D	BP	100
CDR31BP5R6B	5.6	B,C,D	BP	100
CDR31BP6R2B	6.2	B,C,D	BP	100
CDR31BP6R8B	6.8	B,C,D	BP	100
CDR31BP7R5B	7.5	B,C,D	BP	100
CDR31BP8R2B	8.2	B,C,D	BP	100
CDR31BP9R1B	9.1	B,C,D	BP	100
CDR31BP100B	10	F,J,K	BP	100
CDR31BP110B CDR31BP120B CDR31BP130B CDR31BP150B CDR31BP160B	11	F,J,K	BP	100
	12	F,J,K	BP	100
	13	F,J,K	BP	100
	15	F,J,K	BP	100
	16	F,J,K	BP	100
CDR31BP180B CDR31BP200B CDR31BP220B CDR31BP240B CDR31BP270B	18	F,J,K	BP	100
	20	F,J,K	BP	100
	22	F,J,K	BP	100
	24	F,J,K	BP	100
	27	F,J,K	BP	100
CDR31BP300B CDR31BP330B CDR31BP360B CDR31BP390B CDR31BP430B	30	F,J,K	BP	100
	33	F,J,K	BP	100
	36	F,J,K	BP	100
	39	F,J,K	BP	100
	43	F,J,K	BP	100
CDR31BP470B CDR31BP510B CDR31BP560B CDR31BP620B CDR31BP680B	47	F,J,K	BP	100
	51	F,J,K	BP	100
	56	F,J,K	BP	100
	62	F,J,K	BP	100
	68	F,J,K	BP	100
CDR31BP750B	75	F,J,K	BP	100
CDR31BP820B	82	F,J,K	BP	100
CDR31BP910B	91	F,J,K	BP	100

— Add appropriate failure rate

 — Add appropriate termination finish

 — Capacitance Tolerance

		T		
Military Type Designation <u>1</u> /	Capacitance in pF	Capacitance tolerance	Rated temperature and voltage- temperature limits	WVDC
AVX Style 0	805/CDR31	(BP) cont	'd	
CDR31BP101B	100	F,J,K	BP	100
CDR31BP111B	110	F,J,K	BP	100
CDR31BP121B	120	F,J,K	BP	100
CDR31BP131B	130	F,J,K	BP	100
CDR31BP151B	150	F,J,K	BP	100
CDR31BP161B	160	F,J,K	BP	100
CDR31BP181B	180	F,J,K	BP	100
CDR31BP201B	200	F,J,K	BP	100
CDR31BP221B	220	F,J,K	BP	100
CDR31BP241B	240	F,J,K	BP	100
CDR31BP271B	270	F,J,K	BP	100
CDR31BP301B	300	F,J,K	BP	100
CDR31BP331B	330	F,J,K	BP	100
CDR31BP361B	360	F,J,K	BP	100
CDR31BP391B	390	F,J,K	BP	100
CDR31BP431B CDR31BP471B CDR31BP511A CDR31BP561A CDR31BP621A CDR31BP681A	430 470 510 560 620 680	F,J,K F,J,K F,J,K F,J,K F,J,K	BP BP BP BP BP	100 100 50 50 50 50
AVX Style 0	805/CDR31	(BX)		
CDR31BX471B	470	K,M	BX	100
CDR31BX561B	560	K,M	BX	100
CDR31BX681B	680	K,M	BX	100
CDR31BX821B	820	K,M	BX	100
CDR31BX102B	1,000	K,M	BX	100
CDR31BX122B	1,200	K,M	BX	100
CDR31BX152B	1,500	K,M	BX	100
CDR31BX182B	1,800	K,M	BX	100
CDR31BX222B	2,200	K,M	BX	100
CDR31BX272B	2,700	K,M	BX	100
CDR31BX332B	3,300	K,M	BX	100
CDR31BX392B	3,900	K,M	BX	100
CDR31BX472B	4,700	K,M	BX	100
CDR31BX562A	5,600	K,M	BX	50
CDR31BX682A	6,800	K,M	BX	50
CDR31BX822A CDR31BX103A CDR31BX123A CDR31BX153A CDR31BX183A	8,200 10,000 12,000 15,000 18,000	K,M K,M K,M K,M	BX BX BX BX BX	50 50 50 50 50

Add appropriate failure rateAdd appropriate termination finish



 $[\]underline{\bf 1} / {\hbox{The complete part number will include additional symbols to indicate capacitance tolerance, termination and failure rate level.}$



Military Part Number Identification CDR32

CDR32 to MIL-PRF-55681/8

Military Type Designation <u>1</u> /	Capacitance in pF	Capacitance tolerance	Rated temperature and voltage-temperature limits	WVDC
AVX Style 12	206/CDR32	(BP)		
CDR32BP1R0B CDR32BP1R1B CDR32BP1R2B CDR32BP1R3B CDR32BP1R5B	1.0 1.1 1.2 1.3 1.5	B,C B,C B,C B,C B,C	BP BP BP BP	100 100 100 100 100
CDR32BP1R6B	1.6	B,C	BP	100
CDR32BP1R8B	1.8	B,C	BP	100
CDR32BP2R0B	2.0	B,C	BP	100
CDR32BP2R2B	2.2	B,C	BP	100
CDR32BP2R4B	2.4	B,C	BP	100
CDR32BP2R7B CDR32BP3R0B CDR32BP3R3B CDR32BP3R6B CDR32BP3R9B	2.7	B,C,D	BP	100
	3.0	B,C,D	BP	100
	3.3	B,C,D	BP	100
	3.6	B,C,D	BP	100
	3.9	B,C,D	BP	100
CDR32BP4R3B	4.3	B,C,D	BP	100
CDR32BP4R7B	4.7	B,C,D	BP	100
CDR32BP5R1B	5.1	B,C,D	BP	100
CDR32BP5R6B	5.6	B,C,D	BP	100
CDR32BP6R2B	6.2	B,C,D	BP	100
CDR32BP6R8B	6.8	B,C,D	BP	100
CDR32BP7R5B	7.5	B,C,D	BP	100
CDR32BP8R2B	8.2	B,C,D	BP	100
CDR32BP9R1B	9.1	B,C,D	BP	100
CDR32BP100B	10	F,J,K	BP	100
CDR32BP110B	11	F,J,K	BP	100
CDR32BP120B	12	F,J,K	BP	100
CDR32BP130B	13	F,J,K	BP	100
CDR32BP150B	15	F,J,K	BP	100
CDR32BP160B	16	F,J,K	BP	100
CDR32BP180B	18	F,J,K	BP	100
CDR32BP200B	20	F,J,K	BP	100
CDR32BP220B	22	F,J,K	BP	100
CDR32BP240B	24	F,J,K	BP	100
CDR32BP270B	27	F,J,K	BP	100
CDR32BP300B	30	F,J,K	BP	100
CDR32BP330B	33	F,J,K	BP	100
CDR32BP360B	36	F,J,K	BP	100
CDR32BP390B	39	F,J,K	BP	100
CDR32BP430B	43	F,J,K	BP	100
CDR32BP470B	47	F,J,K	BP	100
CDR32BP510B	51	F,J,K	BP	100
CDR32BP560B	56	F,J,K	BP	100
CDR32BP620B	62	F,J,K	BP	100
CDR32BP680B	68	F,J,K	BP	100
CDR32BP750B	75	F,J,K	BP	100
CDR32BP820B	82	F,J,K	BP	100
CDR32BP910B	91	F,J,K	BP	100

Add appropriate failure rate

 Add appropriate termination finish

 Capacitance Tolerance

Military			Rated temperature	WVDC
Type Designation <u>1</u> /	Capacitance in pF	Capacitance tolerance	and voltage- temperature limits	******
AVX Style 1	206/CDR32	(BP) cont	'd	
CDR32BP101B	100	F,J,K	BP	100
CDR32BP111B	110	F,J,K	BP	100
CDR32BP121B	120	F,J,K	BP	100
CDR32BP131B	130	F,J,K	BP	100
CDR32BP151B	150	F,J,K	BP	100
CDR32BP161B	160	F,J,K	BP	100
CDR32BP181B	180	F,J,K	BP	100
CDR32BP201B	200	F,J,K	BP	100
CDR32BP221B	220	F,J,K	BP	100
CDR32BP241B	240	F,J,K	BP	100
CDR32BP271B	270	F,J,K	BP	100
CDR32BP301B	300	F,J,K	BP	100
CDR32BP331B	330	F,J,K	BP	100
CDR32BP361B	360	F,J,K	BP	100
CDR32BP391B	390	F,J,K	BP	100
CDR32BP431B	430	F,J,K	BP	100
CDR32BP471B	470	F,J,K	BP	100
CDR32BP511B	510	F,J,K	BP	100
CDR32BP561B	560	F,J,K	BP	100
CDR32BP621B	620	F,J,K	BP	100
CDR32BP681B	680	F,J,K	BP	100
CDR32BP751B	750	F,J,K	BP	100
CDR32BP821B	820	F,J,K	BP	100
CDR32BP911B	910	F,J,K	BP	100
CDR32BP102B	1,000	F,J,K	BP	100
CDR32BP112A	1,100	F,J,K	BP	50
CDR32BP122A	1,200	F,J,K	BP	50
CDR32BP132A	1,300	F,J,K	BP	50
CDR32BP152A	1,500	F,J,K	BP	50
CDR32BP162A	1,600	F,J,K	BP	50
CDR32BP182A	1,800	F,J,K	BP	50
CDR32BP202A	2,000	F,J,K	BP	50
CDR32BP222A	2,200	F,J,K	BP	50
AVX Style 1	206/CDR32	(BX)		
CDR32BX472B CDR32BX562B CDR32BX682B CDR32BX103B CDR32BX123B CDR32BX153B CDR32BX153B	4,700 5,600 6,800 8,200 10,000	K,M K,M K,M K,M K,M K,M	BX BX BX BX BX BX BX	100 100 100 100 100 100
CDR32BX183A CDR32BX223A CDR32BX273A CDR32BX333A	15,000 18,000 22,000 27,000 33,000	K,M K,M K,M K,M	BX BX BX	50 50 50 50
CDR32BX393A	39,000	K,M	BX	50

Add appropriate failure rate

Add appropriate termination finish



 $[\]underline{\mathbf{1}}/$ The complete part number will include additional symbols to indicate capacitance tolerance, termination and failure rate level.



Military Part Number Identification CDR33/34/35

CDR33/34/35 to MIL-PRF-55681/9/10/11

Military Type Designation <u>1</u> /	Capacitance in pF	Capacitance tolerance	Rated temperature and voltage-temperature limits	WVDC	
AVX Style 1	210/CDR33	(BP)			
CDR33BP102B CDR33BP112B CDR33BP122B CDR33BP152B CDR33BP152B CDR33BP182B CDR33BP202B CDR33BP222B CDR33BP222A CDR33BP272A CDR33BP372A CDR33BP302A	1,000 1,100 1,200 1,300 1,500 1,600 1,800 2,000 2,200 2,400 2,700 3,000	F,J,K F,J,K F,J,K F,J,K F,J,K F,J,K F,J,K F,J,K F,J,K F,J,K	BP BP BP BP BP BP BP BP BP	100 100 100 100 100 100 100 100 50 50	
CDR33BP332A	3,300	F,J,K	BP	50	
AVX Style 1	210/CDR33	(BX)	l		
CDR33BX153B CDR33BX183B CDR33BX223B CDR33BX273B CDR33BX393A CDR33BX473A CDR33BX563A	15,000 18,000 22,000 27,000 39,000 47,000 56,000	K,M K,M K,M K,M K,M K,M	BX BX BX BX BX BX BX	100 100 100 100 50 50	
CDR33BX683A CDR33BX823A CDR33BX104A	68,000 82,000 100,000	K,M K,M K,M	BX BX BX	50 50 50	
AVX Style 1	812/CDR34	(BP)	I		
CDR34BP222B CDR34BP242B CDR34BP372B CDR34BP332B CDR34BP332B CDR34BP332B CDR34BP332B CDR34BP332B	2,200 2,400 2,700 3,000 3,300 3,600 3,900 4,300	F,J,K F,J,K F,J,K F,J,K F,J,K F,J,K F,J,K	BP BP BP BP BP BP BP	100 100 100 100 100 100 100	
CDR34BP472B CDR34BP512A	4,700 5,100	F,J,K F,J,K	BP BP	100 50	
CDR34BP562A CDR34BP622A CDR34BP682A CDR34BP752A CDR34BP822A	5,600 6,200 6,800 7,500 8,200	F,J,K F,J,K F,J,K F,J,K	BP BP BP BP	50 50 50 50 50	
CDR34BP912A CDR34BP103A	9,100 10,000	F,J,K F,J,K	BP BP	50 50	
Add appropriate failure rate Add appropriate termination finish					

Capacitance Tolerance

		Г	ı	
Military Type Designation <u>1</u> /	Capacitance in pF	Capacitance tolerance	Rated temperature and voltage-temperature limits	WVDC
AVX Style 18	812/CDR34	(BX)		
CDR34BX273B CDR34BX333B CDR34BX473B CDR34BX563B CDR34BX104A CDR34BX124A CDR34BX154A CDR34BX184A	27,000 33,000 39,000 47,000 56,000 100,000 120,000 150,000 180,000	K,M K,M K,M K,M K,M K,M K,M	BX BX BX BX BX BX BX BX BX	100 100 100 100 100 50 50 50
AVX Style 1	825/CDR35	(BP)		
CDR35BP472B CDR35BP562B CDR35BP62B CDR35BP682B CDR35BP752B CDR35BP822B CDR35BP912B CDR35BP912B CDR35BP13A CDR35BP13A CDR35BP153A CDR35BP163A CDR35BP183A CDR35BP183A CDR35BP183A CDR35BP23A	4,700 5,100 5,600 6,200 6,800 7,500 8,200 9,100 10,000 11,000 12,000 13,000 16,000 18,000 20,000 22,000	F,J,K F,J,K F,J,K F,J,K F,J,K F,J,K F,J,K F,J,K F,J,K F,J,K F,J,K F,J,K F,J,K F,J,K	BP BP BP BP BP BP BP BP BP BP BP BP BP B	100 100 100 100 100 100 100 100 50 50 50 50 50 50
AVX Style 18	825/CDR35	(BX)		
CDR35BX563B CDR35BX823B CDR35BX104B CDR35BX124B CDR35BX154B CDR35BX154B CDR35BX224A CDR35BX274A CDR35BX334A CDR35BX394A CDR35BX394A CDR35BXX474A	56,000 68,000 82,000 100,000 120,000 150,000 180,000 220,000 270,000 330,000 470,000	K,M K,M K,M K,M K,M K,M K,M K,M K,M K,M	BX BX BX BX BX BX BX BX BX BX BX BX	100 100 100 100 100 100 50 50 50 50 50

Add appropriate failure rate

- Add appropriate termination finish



 $[\]underline{\bf 1}/$ The complete part number will include additional symbols to indicate capacitance tolerance, termination and failure rate level.

Packaging of Chip Components



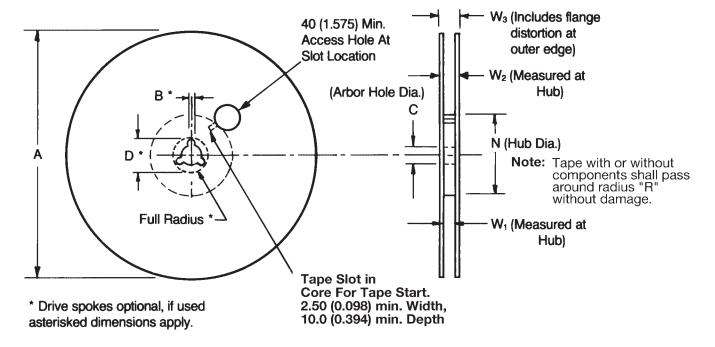
Automatic Insertion Packaging

TAPE & REEL QUANTITIES

All tape and reel specifications are in compliance with RS481.

	8mm	12	mm
Paper or Embossed Carrier	0612, 0508, 0805, 1206, 1210		
Embossed Only	0306	1808	1812, 1825 2220, 2225
Paper Only	0201, 0402, 0603		
Qty. per Reel/7" Reel	2,000, 3,000 or 4,000, 10,000, 15,000 Contact factory for exact quantity	3,000	500, 1,000 Contact factory for exact quantity
Qty. per Reel/13" Reel	5,000, 10,000, 50,000 Contact factory for exact quantity	10,000	4,000

REEL DIMENSIONS



Tape Size ⁽¹⁾	A Max.	B* Min.	С	D* Min.	N Min.	W ₁	W ₂ Max.	W ₃
8mm	330	1.5	13.0 +0.50	20.2	50.0	8.40 ^{+1.5} (0.331 ^{+0.059})	14.4 (0.567)	7.90 Min. (0.311) 10.9 Max. (0.429)
12mm	(12.992)	(0.059)	(0.512 -0.008)	(0.795)	(1.969)	12.4 ^{+2.0} (0.488 ^{+0.079})	18.4 (0.724)	11.9 Min. (0.469) 15.4 Max. (0.607)

Metric dimensions will govern.

English measurements rounded and for reference only.

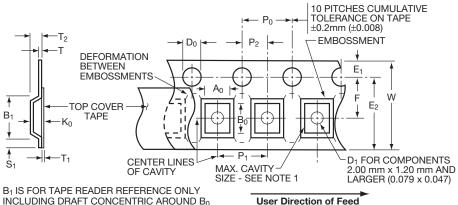
⁽¹⁾ For tape sizes 16mm and 24mm (used with chip size 3640) consult EIA RS-481 latest revision.



Embossed Carrier Configuration



8 & 12mm Tape Only



INCLUDING DRAFT CONCENTRIC AROUND Bo

8 & 12mm Embossed Tape **Metric Dimensions Will Govern**

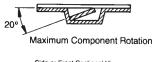
CONSTANT DIMENSIONS

Tape Size	D ₀	E	P ₀	P ₂	S ₁ Min.	T Max.	T ₁
8mm and 12mm	1.50 ^{+0.10} _{-0.0} (0.059 ^{+0.004})	1.75 ± 0.10 (0.069 ± 0.004)	4.0 ± 0.10 (0.157 ± 0.004)	$2.0 \pm 0.05 \\ (0.079 \pm 0.002)$	0.60 (0.024)	0.60 (0.024)	0.10 (0.004) Max.

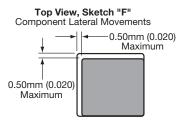
VARIABLE DIMENSIONS

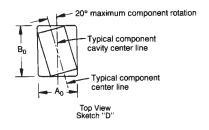
Tape Size	B₁ Max.	D₁ Min.	E ₂ Min.	F	P ₁ See Note 5	R Min. See Note 2	T ₂	W Max.	$A_0 B_0 K_0$
8mm	4.35 (0.171)	1.00 (0.039)	6.25 (0.246)	3.50 ± 0.05 (0.138 ± 0.002)	4.00 ± 0.10 (0.157 ± 0.004)	25.0 (0.984)	2.50 Max. (0.098)	8.30 (0.327)	See Note 1
12mm	8.20 (0.323)	1.50 (0.059)	10.25 (0.404)	5.50 ± 0.05 (0.217 ± 0.002)	4.00 ± 0.10 (0.157 ± 0.004)	30.0 (1.181)	6.50 Max. (0.256)	12.3 (0.484)	See Note 1
8mm 1/2 Pitch	4.35 (0.171)	1.00 (0.039)	6.25 (0.246)	3.50 ± 0.05 (0.138 ± 0.002)	2.00 ± 0.10 (0.079 ± 0.004)	25.0 (0.984)	2.50 Max. (0.098)	8.30 (0.327)	See Note 1
12mm Double Pitch	8.20 (0.323)	1.50 (0.059)	10.25 (0.404)	5.50 ± 0.05 (0.217 ± 0.002)	8.00 ± 0.10 (0.315 ± 0.004)	30.0 (1.181)	6.50 Max. (0.256)	12.3 (0.484)	See Note 1

- 1. The cavity defined by A₀, B₀, and K₀ shall be configured to provide the following: Surround the component with sufficient clearance such that:
 - a) the component does not protrude beyond the sealing plane of the cover tape.
 - b) the component can be removed from the cavity in a vertical direction without mechanical restriction, after the cover tape has been removed.
 - c) rotation of the component is limited to 20° maximum (see Sketches D & E).
 - d) lateral movement of the component is restricted to 0.5mm maximum (see Sketch F).
- 2. Tape with or without components shall pass around radius "R" without damage.
- 3. Bar code labeling (if required) shall be on the side of the reel opposite the round sprocket holes. Refer to EIA-556.
- 4. B₁ dimension is a reference dimension for tape feeder clearance only.
- 5. If $P_1 = 2.0$ mm, the tape may not properly index in all tape feeders



Side or Front Sectional View Sketch "C"



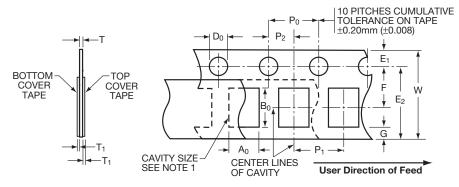




Paper Carrier Configuration



8 & 12mm Tape Only



8 & 12mm Paper Tape Metric Dimensions Will Govern

CONSTANT DIMENSIONS

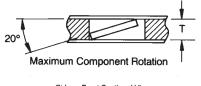
Tape Size	D ₀	E	P ₀	P ₂	T ₁	G. Min.	R Min.
8mm and 12mm	1.50 ^{+0.10} _{-0.0} (0.059 ^{+0.004})	1.75 ± 0.10 (0.069 ± 0.004)	$4.00 \pm 0.10 \\ (0.157 \pm 0.004)$	2.00 ± 0.05 (0.079 ± 0.002)	0.10 (0.004) Max.	0.75 (0.030) Min.	25.0 (0.984) See Note 2 Min.

VARIABLE DIMENSIONS

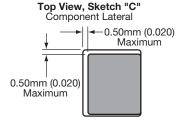
Tape Size	P ₁ See Note 4	E ₂ Min.	F	W	$A_0 B_0$	Т
8mm	4.00 ± 0.10 (0.157 ± 0.004)	6.25 (0.246)	$3.50 \pm 0.05 \\ (0.138 \pm 0.002)$	8.00 ^{+0.30} -0.10 (0.315 ^{+0.012})	See Note 1	1.10mm
12mm	4.00 ± 0.010 (0.157 ± 0.004)	10.25 (0.404)	5.50 ± 0.05 (0.217 ± 0.002)	12.0 ± 0.30 (0.472 ± 0.012)		(0.043) Max. for Paper Base Tape and
8mm 1/2 Pitch	2.00 ± 0.05 (0.079 ± 0.002)	6.25 (0.246)	3.50 ± 0.05 (0.138 ± 0.002)	8.00 ±0.30 (0.315 ±0.0012)		1.60mm (0.063) Max. for Non-Paper Base Compositions
12mm Double Pitch	8.00 ± 0.10 (0.315 ± 0.004)	10.25 (0.404)	5.50 ± 0.05 (0.217 ± 0.002)	12.0 ± 0.30 (0.472 ± 0.012)		Dase Compositions

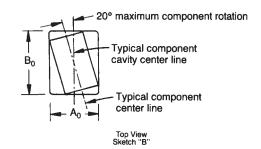
NOTES

- 1. The cavity defined by A_0 , B_0 , and T shall be configured to provide sufficient clearance surrounding the component so that:
 - a) the component does not protrude beyond either surface of the carrier tape; b) the component can be removed from the cavity in a vertical direction without
 - mechanical restriction after the top cover tape has been removed; c) rotation of the component is limited to 20° maximum (see Sketches A & B);
 - d) lateral movement of the component is restricted to 0.5mm maximum (see Sketch C).
- 2. Tape with or without components shall pass around radius "R" without damage.
- Bar code labeling (if required) shall be on the side of the reel opposite the sprocket holes. Refer to EIA-556.
- 4. If $P_1 = 2.0$ mm, the tape may not properly index in all tape feeders.



Side or Front Sectional View Sketch "A"





Bar Code Labeling Standard

AVX bar code labeling is available and follows latest version of EIA-556



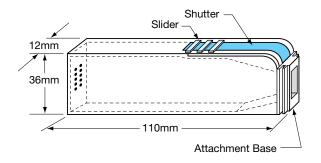
Bulk Case Packaging



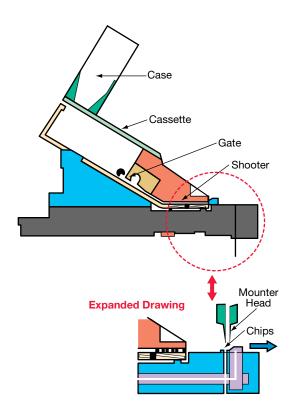
BENEFITS

- Easier handling
- Smaller packaging volume (1/20 of T/R packaging)
- Easier inventory control
- Flexibility
- Recyclable

CASE DIMENSIONS



BULK FEEDER



CASE QUANTITIES

Part Size	0402	0603	0805	1206
Qty. (pcs / cassette)	80,000	15,000	10,000 (T=.023") 8,000 (T=.031") 6,000 (T=.043")	5,000 (T=.023") 4,000 (T=.032") 3,000 (T=.044")



Basic Capacitor Formulas



I. Capacitance (farads)

English:
$$C = \frac{.224 \text{ K A}}{T_D}$$

Metric: $C = \frac{.0884 \text{ K A}}{T_D}$

II. Energy stored in capacitors (Joules, watt - sec)

III. Linear charge of a capacitor (Amperes)

$$I = C \frac{dV}{dt}$$

IV. Total Impedance of a capacitor (ohms)

$$Z = \sqrt{R_S^2 + (X_C - X_L)^2}$$

V. Capacitive Reactance (ohms)

$$x_C = \frac{1}{2 \pi fC}$$

VI. Inductive Reactance (ohms)

$$x_L = 2 \pi fL$$

VII. Phase Angles:

Ideal Capacitors: Current leads voltage 90° Ideal Inductors: Current lags voltage 90° Ideal Resistors: Current in phase with voltage

VIII. Dissipation Factor (%)

D.F.=
$$\tan \delta$$
 (loss angle) = $\frac{\text{E.S.R.}}{\text{X}_{\text{C}}}$ = (2 π fC) (E.S.R.)

IX. Power Factor (%)

P.F. = Sine δ (loss angle) = Cos ϕ (phase angle) P.F. = (when less than 10%) = DF

X. Quality Factor (dimensionless)

Q = Cotan
$$\delta$$
 (loss angle) = $\frac{1}{D.F.}$

XI. Equivalent Series Resistance (ohms)

E.S.R. = (D.F.) (Xc) = (D.F.) / (2
$$\pi$$
 fC)

XII. Power Loss (watts)

Power Loss =
$$(2 \pi fCV^2)$$
 (D.F.)

XIII. KVA (Kilowatts)

$$KVA = 2 \pi fCV^2 \times 10^{-3}$$

XIV. Temperature Characteristic (ppm/°C)

$$T.C. = \frac{Ct - C_{25}}{C_{25} (T_t - 25)} \times 10^6$$

XV. Cap Drift (%)

C.D. =
$$\frac{C_1 - C_2}{C_1}$$
 x 100

XVI. Reliability of Ceramic Capacitors
$$\overset{L_o}{\bar{L}_t} = \left(\frac{V_t}{V_o} \right) \overset{X}{X} \quad \left(\frac{T_t}{T_o} \right) \overset{Y}{X}$$

XVII. Capacitors in Series (current the same)

Any Number:
$$\frac{1}{C_T} = \frac{1}{C_1} + \frac{1}{C_2} - \frac{1}{C_N}$$

Two: $C_T = \frac{C_1 C_2}{C_1 + C_2}$

XVIII. Capacitors in Parallel (voltage the same)

$$C_T = C_1 + C_2 - - + C_N$$

XIX. Aging Rate

A.R. = $\%\Delta$ C/decade of time

XX. Decibels

$$db = 20 log \frac{V_1}{V_2}$$

METRIC PREFIXES SYMBOLS

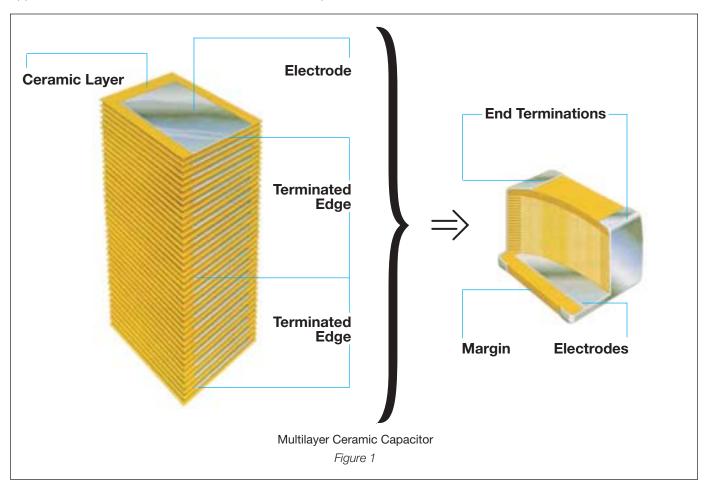
Pico	X 10 ⁻¹²
Nano	X 10 ⁻⁹
Micro	X 10 ⁻⁶
Milli	X 10 ⁻³
Deci	X 10 ⁻¹
Deca	X 10 ⁺¹
Kilo	X 10 ⁺³
Mega	X 10 ⁺⁶
Giga	X 10 ⁺⁹
Tera	X 10 ⁺¹²





Basic Construction - A multilayer ceramic (MLC) capacitor is a monolithic block of ceramic containing two sets of offset, interleaved planar electrodes that extend to two opposite surfaces of the ceramic dielectric. This simple

structure requires a considerable amount of sophistication, both in material and manufacture, to produce it in the quality and quantities needed in today's electronic equipment.



Formulations - Multilayer ceramic capacitors are available in both Class 1 and Class 2 formulations. Temperature compensating formulation are Class 1 and temperature stable and general application formulations are classified as Class 2.

Class 1 – Class 1 capacitors or temperature compensating capacitors are usually made from mixtures of titanates where barium titanate is normally not a major part of the mix. They have predictable temperature coefficients and in general, do not have an aging characteristic. Thus they are the most stable capacitor available. The most popular Class 1 multilayer ceramic capacitors are COG (NPO) temperature compensating capacitors (negative-positive 0 ppm/°C).

Class 2 – EIA Class 2 capacitors typically are based on the chemistry of barium titanate and provide a wide range of capacitance values and temperature stability. The most commonly used Class 2 dielectrics are X7R and Y5V. The X7R provides intermediate capacitance values which vary only ±15% over the temperature range of -55°C to 125°C. It finds applications where stability over a wide temperature range is required.

The Y5V provides the highest capacitance values and is used in applications where limited temperature changes are expected. The capacitance value for Y5V can vary from 22% to -82% over the -30°C to 85°C temperature range. The Z5U dielectric is between X7R and Y5V in both stability and capacitance range.

All Class 2 capacitors vary in capacitance value under the influence of temperature, operating voltage (both AC and DC), and frequency. For additional information on performance changes with operating conditions, consult AVX's software, SpiCap.





Table 1: EIA and MIL Temperature Stable and General Application Codes

EIA CODE Percent Capacity Change Over Temperature Range						
RS198	Temperature Range					
X7	-55°C to +125°C					
X5	-55°C to +85°C					
Y5	-30°C to +85°C					
Z5	+10°C to +85°C					
Code	Percent Capacity Change					
D	±3.3%					
E	±4.7%					
F	±7.5%					
Р	±10%					
R	±15%					
S	±22%					
T	+22%, -33%					
Ü	+22%, - 56%					
V	+22%, -82%					

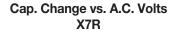
EXAMPLE – A capacitor is desired with the capacitance value at 25°C to increase no more than 7.5% or decrease no more than 7.5% from -30°C to +85°C. EIA Code will be Y5F.

	MIL CODE								
Symbol	bol Temperature Range								
A B C	-55°C to +85°C -55°C to +125°C -55°C to +150°C								
Symbol	Cap. Change Zero Volts Cap. Change Rated Volts								
R W X Y Z	+15%, -15% +22%, -56% +15%, -15% +30%, -70% +20%, -20%	+15%, -40% +22%, -66% +15%, -25% +30%, -80% +20%, -30%							

Temperature characteristic is specified by combining range and change symbols, for example BR or AW. Specification slash sheets indicate the characteristic applicable to a given style of capacitor.

In specifying capacitance change with temperature for Class 2 materials, EIA expresses the capacitance change over an operating temperature range by a 3 symbol code. The first symbol represents the cold temperature end of the temperature range, the second represents the upper limit of the operating temperature range and the third symbol represents the capacitance change allowed over the operating temperature range. Table 1 provides a detailed explanation of the EIA system.

Effects of Voltage – Variations in voltage have little effect on Class 1 dielectric but does affect the capacitance and dissipation factor of Class 2 dielectrics. The application of DC voltage reduces both the capacitance and dissipation factor while the application of an AC voltage within a reasonable range tends to increase both capacitance and dissipation factor readings. If a high enough AC voltage is applied, eventually it will reduce capacitance just as a DC voltage will. Figure 2 shows the effects of AC voltage.



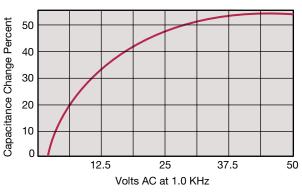
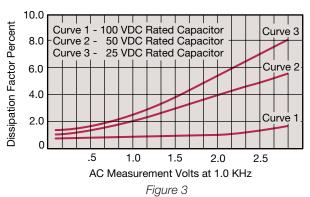


Figure 2

Capacitor specifications specify the AC voltage at which to measure (normally 0.5 or 1 VAC) and application of the wrong voltage can cause spurious readings. Figure 3 gives the voltage coefficient of dissipation factor for various AC voltages at 1 kilohertz. Applications of different frequencies will affect the percentage changes versus voltages.

D.F. vs. A.C. Measurement Volts X7R

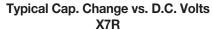


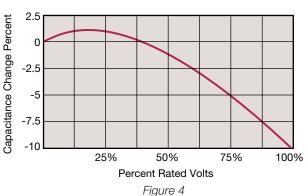
shown in Figure 5 for the military BX characteristic.

Typical effect of the application of DC voltage is shown in Figure 4. The voltage coefficient is more pronounced for higher K dielectrics. These figures are shown for room temperature conditions. The combination characteristic known as voltage temperature limits which shows the effects of rated voltage over the operating temperature range is

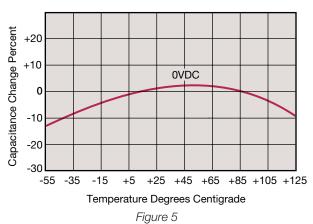








Typical Cap. Change vs. Temperature X7R



Effects of Time - Class 2 ceramic capacitors change capacitance and dissipation factor with time as well as temperature, voltage and frequency. This change with time is known as aging. Aging is caused by a gradual re-alignment of the crystalline structure of the ceramic and produces an exponential loss in capacitance and decrease in dissipation factor versus time. A typical curve of aging rate for semistable ceramics is shown in Figure 6.

If a Class 2 ceramic capacitor that has been sitting on the shelf for a period of time, is heated above its curie point, (125°C for 4 hours or 150°C for ½ hour will suffice) the part will de-age and return to its initial capacitance and dissipation factor readings. Because the capacitance changes rapidly, immediately after de-aging, the basic capacitance measurements are normally referred to a time period sometime after the de-aging process. Various manufacturers use different time bases but the most popular one is one day or twenty-four hours after "last heat." Change in the aging curve can be caused by the application of voltage and other stresses. The possible changes in capacitance due to de-aging by heating the unit explain why capacitance changes are allowed after test, such as temperature cycling, moisture resistance, etc., in MIL specs. The application of high voltages such as dielectric withstanding voltages also

tends to de-age capacitors and is why re-reading of capacitance after 12 or 24 hours is allowed in military specifications after dielectric strength tests have been performed.

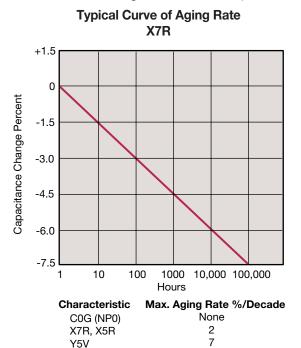


Figure 6

Effects of Frequency – Frequency affects capacitance and impedance characteristics of capacitors. This effect is much more pronounced in high dielectric constant ceramic formulation that is low K formulations. AVX's SpiCap software generates impedance, ESR, series inductance, series resonant frequency and capacitance all as functions of frequency, temperature and DC bias for standard chip sizes and styles. It is available free from AVX and can be downloaded for free from AVX website: www.avxcorp.com.







Effects of Mechanical Stress - High "K" dielectric ceramic capacitors exhibit some low level piezoelectric reactions under mechanical stress. As a general statement, the piezoelectric output is higher, the higher the dielectric constant of the ceramic. It is desirable to investigate this effect before using high "K" dielectrics as coupling capacitors in extremely low level applications.

Reliability - Historically ceramic capacitors have been one of the most reliable types of capacitors in use today. The approximate formula for the reliability of a ceramic capacitor is:

$$\frac{L_o}{L_t} = \left(\frac{V_t}{V_o}\right)^X \left(\frac{T_t}{T_o}\right)^Y$$

where

 L_o = operating life **L**_t = test life

 $\begin{aligned} \textbf{T}_{\textbf{t}} &= \text{test temperature and} \\ \textbf{T}_{\textbf{o}} &= \text{operating temperature} \end{aligned}$

 V_t = test voltage

V_o = operating voltage X,Y = see text

Historically for ceramic capacitors exponent X has been considered as 3. The exponent Y for temperature effects typically tends to run about 8.

A capacitor is a component which is capable of storing electrical energy. It consists of two conductive plates (electrodes) separated by insulating material which is called the dielectric. A typical formula for determining capacitance is:

$$C = \frac{.224 \text{ KA}}{t}$$

C = capacitance (picofarads)

K = dielectric constant (Vacuum = 1)

A = area in square inches

t = separation between the plates in inches (thickness of dielectric)

.224 = conversion constant

(.0884 for metric system in cm)

Capacitance - The standard unit of capacitance is the farad. A capacitor has a capacitance of 1 farad when 1 coulomb charges it to 1 volt. One farad is a very large unit and most capacitors have values in the micro (10-6), nano (10⁻⁹) or pico (10⁻¹²) farad level.

Dielectric Constant – In the formula for capacitance given above the dielectric constant of a vacuum is arbitrarily chosen as the number 1. Dielectric constants of other materials are then compared to the dielectric constant of a vacuum.

Dielectric Thickness - Capacitance is indirectly proportional to the separation between electrodes. Lower voltage requirements mean thinner dielectrics and greater capacitance per volume.

Area - Capacitance is directly proportional to the area of the electrodes. Since the other variables in the equation are usually set by the performance desired, area is the easiest parameter to modify to obtain a specific capacitance within a material group.

Energy Stored - The energy which can be stored in a capacitor is given by the formula:

$$E = \frac{1}{2}CV^2$$

E = energy in joules (watts-sec)

V = applied voltage

C = capacitance in farads

Potential Change - A capacitor is a reactive component which reacts against a change in potential across it. This is shown by the equation for the linear charge of a capacitor:

$$I_{ideal} = C \frac{dV}{dt}$$

where

I = Current

C = Capacitance

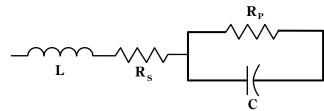
dV/dt = Slope of voltage transition across capacitor

Thus an infinite current would be required to instantly change the potential across a capacitor. The amount of current a capacitor can "sink" is determined by the above equation.

Equivalent Circuit - A capacitor, as a practical device, exhibits not only capacitance but also resistance and inductance. A simplified schematic for the equivalent circuit

C = Capacitance $\mathbf{R}_{\mathbf{s}}$ = Series Resistance **L** = Inductance

 $\mathbf{R}_{\mathbf{p}}$ = Parallel Resistance



Reactance – Since the insulation resistance (R_n) is normally very high, the total impedance of a capacitor is:

$$Z = \sqrt{R_s^2 + (X_c - X_L)^2}$$
 where

Z = Total Impedance

 $\mathbf{R_s}$ = Series Resistance $\mathbf{X_c}$ = Capacitive Reactance =

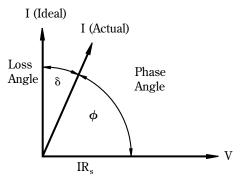
 X_i = Inductive Reactance = $2 \pi fL$

The variation of a capacitor's impedance with frequency determines its effectiveness in many applications.

Phase Angle - Power Factor and Dissipation Factor are often confused since they are both measures of the loss in a capacitor under AC application and are often almost identical in value. In a "perfect" capacitor the current in the capacitor will lead the voltage by 90°.





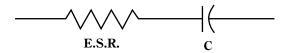


In practice the current leads the voltage by some other phase angle due to the series resistance $R_{\rm s}$. The complement of this angle is called the loss angle and:

Power Factor (P.F.) = Cos ϕ or Sine δ Dissipation Factor (D.F.) = $\tan \delta$

for small values of δ the tan and sine are essentially equal which has led to the common interchangeability of the two terms in the industry.

Equivalent Series Resistance - The term E.S.R. or Equivalent Series Resistance combines all losses both series and parallel in a capacitor at a given frequency so that the equivalent circuit is reduced to a simple R-C series connection.



Dissipation Factor - The DF/PF of a capacitor tells what percent of the apparent power input will turn to heat in the capacitor.

Dissipation Factor =
$$\frac{\text{E.S.R.}}{\text{X}_c}$$
 = (2 π fC) (E.S.R.)

The watts loss are:

Watts loss =
$$(2 \pi fCV^2)$$
 (D.F.)

Very low values of dissipation factor are expressed as their reciprocal for convenience. These are called the "Q" or Quality factor of capacitors.

Parasitic Inductance - The parasitic inductance of capacitors is becoming more and more important in the decoupling of today's high speed digital systems. The relationship between the inductance and the ripple voltage induced on the DC voltage line can be seen from the simple inductance equation:

$$V = L \frac{di}{dt}$$

The $\frac{di}{dt}$ seen in current microprocessors can be as high as 0.3 A/ns, and up to 10A/ns. At 0.3 A/ns, 100pH of parasitic inductance can cause a voltage spike of 30mV. While this does not sound very drastic, with the Vcc for microprocessors decreasing at the current rate, this can be a fairly large percentage.

Another important, often overlooked, reason for knowing the parasitic inductance is the calculation of the resonant frequency. This can be important for high frequency, bypass capacitors, as the resonant point will give the most signal attenuation. The resonant frequency is calculated from the simple equation:

$$f_{\text{res}} = \frac{1}{2\pi\sqrt{LC}}$$

Insulation Resistance - Insulation Resistance is the resistance measured across the terminals of a capacitor and consists principally of the parallel resistance Rp shown in the equivalent circuit. As capacitance values and hence the area of dielectric increases, the I.R. decreases and hence the product (C x IR or RC) is often specified in ohm faradsor more commonly megohm-microfarads. Leakage current is determined by dividing the rated voltage by IR (Ohm's Law).

Dielectric Strength - Dielectric Strength is an expression of the ability of a material to withstand an electrical stress. Although dielectric strength is ordinarily expressed in volts, it is actually dependent on the thickness of the dielectric and thus is also more generically a function of volts/mil.

Dielectric Absorption - A capacitor does not discharge instantaneously upon application of a short circuit, but drains gradually after the capacitance proper has been discharged. It is common practice to measure the dielectric absorption by determining the "reappearing voltage" which appears across a capacitor at some point in time after it has been fully discharged under short circuit conditions.

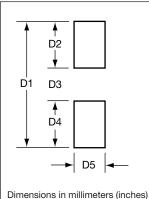
Corona - Corona is the ionization of air or other vapors which causes them to conduct current. It is especially prevalent in high voltage units but can occur with low voltages as well where high voltage gradients occur. The energy discharged degrades the performance of the capacitor and can in time cause catastrophic failures.



MLC Chip Capacitors



REFLOW SOLDERING



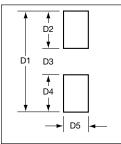
Case Size	D1	D2	D3	D4	D 5
0402	1.70 (0.07)	0.60 (0.02)	0.50 (0.02)	0.60 (0.02)	0.50 (0.02)
0603	2.30 (0.09)	0.80 (0.03)	0.70 (0.03)	0.80 (0.03)	0.75 (0.03)
0805	3.00 (0.12)	1.00 (0.04)	1.00 (0.04)	1.00 (0.04)	1.25 (0.05)
1206	4.00 (0.16)	1.00 (0.04)	2.00 (0.09)	1.00 (0.04)	1.60 (0.06)
1210	4.00 (0.16)	1.00 (0.04)	2.00 (0.09)	1.00 (0.04)	2.50 (0.10)
1808	5.60 (0.22)	1.00 (0.04)	3.60 (0.14)	1.00 (0.04)	2.00 (0.08)
1812	5.60 (0.22)	1.00 (0.04))	3.60 (0.14)	1.00 (0.04)	3.00 (0.12)
1825	5.60 (0.22)	1.00 (0.04)	3.60 (0.14)	1.00 (0.04)	6.35 (0.25)
2220	6.60 (0.26)	1.00 (0.04)	4.60 (0.18)	1.00 (0.04)	5.00 (0.20)
2225	6.60 (0.26)	1.00 (0.04)	4.60 (0.18)	1.00 (0.04)	6.35 (0.25)

Component Pad Design

Component pads should be designed to achieve good solder filets and minimize component movement during reflow soldering. Pad designs are given below for the most common sizes of multilayer ceramic capacitors for both wave and reflow soldering. The basis of these designs is:

- Pad width equal to component width. It is permissible to decrease this to as low as 85% of component width but it is not advisable to go below this.
- Pad overlap 0.5mm beneath component.
- Pad extension 0.5mm beyond components for reflow and 1.0mm for wave soldering.

WAVE SOLDERING

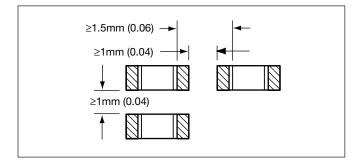


Case Size	D1	D2	D3	D4	D5
0603	3.10 (0.12)	1.20 (0.05)	0.70 (0.03)	1.20 (0.05)	0.75 (0.03)
0805	4.00 (0.15)	1.50 (0.06)	1.00 (0.04)	1.50 (0.06)	1.25 (0.05)
1206	5.00 (0.19)	1.50 (0.06)	2.00 (0.09)	1.50 (0.06)	1.60 (0.06)
1210	5.00 (0.19)	1.50 (0.06)	2.00 (0.09)	1.50 (0.06)	2.50 (0.10)

Dimensions in millimeters (inches)

Component Spacing

For wave soldering components, must be spaced sufficiently far apart to avoid bridging or shadowing (inability of solder to penetrate properly into small spaces). This is less important for reflow soldering but sufficient space must be allowed to enable rework should it be required.



Preheat & Soldering

The rate of preheat should not exceed 4°C/second to prevent thermal shock. A better maximum figure is about 2°C/second.

For capacitors size 1206 and below, with a maximum thickness of 1.25mm, it is generally permissible to allow a temperature differential from preheat to soldering of 150°C. In all other cases this differential should not exceed 100°C.

For further specific application or process advice, please consult AVX.

Cleaning

Care should be taken to ensure that the capacitors are thoroughly cleaned of flux residues especially the space beneath the capacitor. Such residues may otherwise become conductive and effectively offer a low resistance bypass to the capacitor.

Ultrasonic cleaning is permissible, the recommended conditions being 8 Watts/litre at 20-45 kHz, with a process cycle of 2 minutes vapor rinse, 2 minutes immersion in the ultrasonic solvent bath and finally 2 minutes vapor rinse.



MLC Chip Capacitors



APPLICATION NOTES

Storage

Good solderability is maintained for at least twelve months, provided the components are stored in their "as received" packaging at less than 40°C and 70% RH.

Solderability

Terminations to be well soldered after immersion in a 60/40 tin/lead solder bath at 235 ± 5 °C for 2 ± 1 seconds.

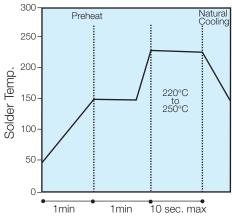
Leaching

Terminations will resist leaching for at least the immersion times and conditions shown below.

Termination Type	Solder	Solder	Immersion Time	
	Tin/Lead/Silver	Temp. °C	Seconds	
Nickel Barrier	60/40/0	260 ± 5	30 ± 1	

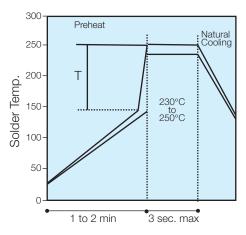
Recommended Soldering Profiles

Reflow



(Minimize soldering time)

Wave



(Preheat chips before soldering) T/maximum 150°C

General

Surface mounting chip multilayer ceramic capacitors are designed for soldering to printed circuit boards or other substrates. The construction of the components is such that they will withstand the time/temperature profiles used in both wave and reflow soldering methods.

Handling

Chip multilayer ceramic capacitors should be handled with care to avoid damage or contamination from perspiration and skin oils. The use of tweezers or vacuum pick ups is strongly recommended for individual components. Bulk handling should ensure that abrasion and mechanical shock are minimized. Taped and reeled components provides the ideal medium for direct presentation to the placement machine. Any mechanical shock should be minimized during handling chip multilayer ceramic capacitors.

Preheat

It is important to avoid the possibility of thermal shock during soldering and carefully controlled preheat is therefore required. The rate of preheat should not exceed 4°C/second and a target figure 2°C/second is recommended. Although an 80°C to 120°C temperature differential is preferred, recent developments allow a temperature differential between the component surface and the soldering temperature of 150°C (Maximum) for capacitors of 1210 size and below with a maximum thickness of 1.25mm. The user is cautioned that the risk of thermal shock increases as chip size or temperature differential increases.

Soldering

Mildly activated rosin fluxes are preferred. The minimum amount of solder to give a good joint should be used. Excessive solder can lead to damage from the stresses caused by the difference in coefficients of expansion between solder, chip and substrate. AVX terminations are suitable for all wave and reflow soldering systems. If hand soldering cannot be avoided, the preferred technique is the utilization of hot air soldering tools.

Cooling

Natural cooling in air is preferred, as this minimizes stresses within the soldered joint. When forced air cooling is used, cooling rate should not exceed 4°C/second. Quenching is not recommended but if used, maximum temperature differentials should be observed according to the preheat conditions above.

Cleaning

Flux residues may be hygroscopic or acidic and must be removed. AVX MLC capacitors are acceptable for use with all of the solvents described in the specifications MIL-STD-202 and EIA-RS-198. Alcohol based solvents are acceptable and properly controlled water cleaning systems are also acceptable. Many other solvents have been proven successful, and most solvents that are acceptable to other components on circuit assemblies are equally acceptable for use with ceramic capacitors.



MLC Chip Capacitors

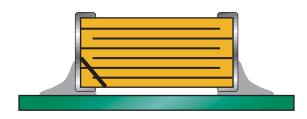


POST SOLDER HANDLING

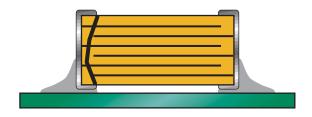
Once SMP components are soldered to the board, any bending or flexure of the PCB applies stresses to the soldered joints of the components. For leaded devices, the stresses are absorbed by the compliancy of the metal leads and generally don't result in problems unless the stress is large enough to fracture the soldered connection.

Ceramic capacitors are more susceptible to such stress because they don't have compliant leads and are brittle in nature. The most frequent failure mode is low DC resistance or short circuit. The second failure mode is significant loss of capacitance due to severing of contact between sets of the internal electrodes.

Cracks caused by mechanical flexure are very easily identified and generally take one of the following two general forms:



Type A: Angled crack between bottom of device to top of solder joint.



Type B: Fracture from top of device to bottom of device.

Mechanical cracks are often hidden underneath the termination and are difficult to see externally. However, if one end termination falls off during the removal process from PCB, this is one indication that the cause of failure was excessive mechanical stress due to board warping.

COMMON CAUSES OF MECHANICAL CRACKING

The most common source for mechanical stress is board depanelization equipment, such as manual breakapart, v-cutters and shear presses. Improperly aligned or dull cutters may cause torqueing of the PCB resulting in flex stresses being transmitted to components near the board edge. Another common source of flexural stress is contact during parametric testing when test points are probed. If the PCB is allowed to flex during the test cycle, nearby ceramic capacitors may be broken.

A third common source is board to board connections at vertical connectors where cables or other PCBs are connected to the PCB. If the board is not supported during the plug/unplug cycle, it may flex and cause damage to nearby components.

Special care should also be taken when handling large (>6" on a side) PCBs since they more easily flex or warp than smaller boards.

REWORKING OF MLCs

Thermal shock is common in MLCs that are manually attached or reworked with a soldering iron. AVX strongly recommends that any reworking of MLCs be done with hot air reflow rather than soldering irons. It is practically impossible to cause any thermal shock in ceramic capacitors when using hot air reflow.

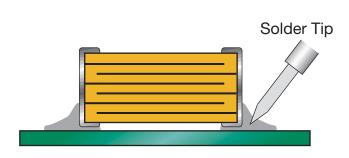
However direct contact by the soldering iron tip often causes thermal cracks that may fail at a later date. If rework by soldering iron is absolutely necessary, it is recommended that the wattage of the iron be less than 30 watts and the tip temperature be <300°C. Rework should be performed by applying the solder iron tip to the pad and not directly contacting any part of the ceramic capacitor.



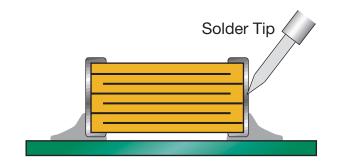


MLC Chip Capacitors





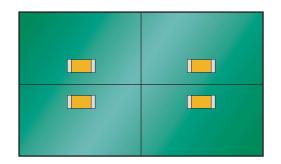




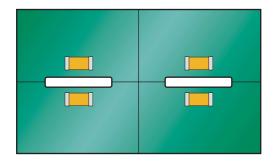
Poor Method - Direct Contact with Part

PCB BOARD DESIGN

To avoid many of the handling problems, AVX recommends that MLCs be located at least .2" away from nearest edge of board. However when this is not possible, AVX recommends that the panel be routed along the cut line, adjacent to where the MLC is located.



No Stress Relief for MLCs



Routed Cut Line Relieves Stress on MLC



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Comprehensive capacitor application software library which includes:

SpiCap (for MLC chip capacitors)

SpiTan (for tantalum capacitors)

SpiCalci (for power supply capacitors)

SpiMic (for RF-Microwave capacitors)

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